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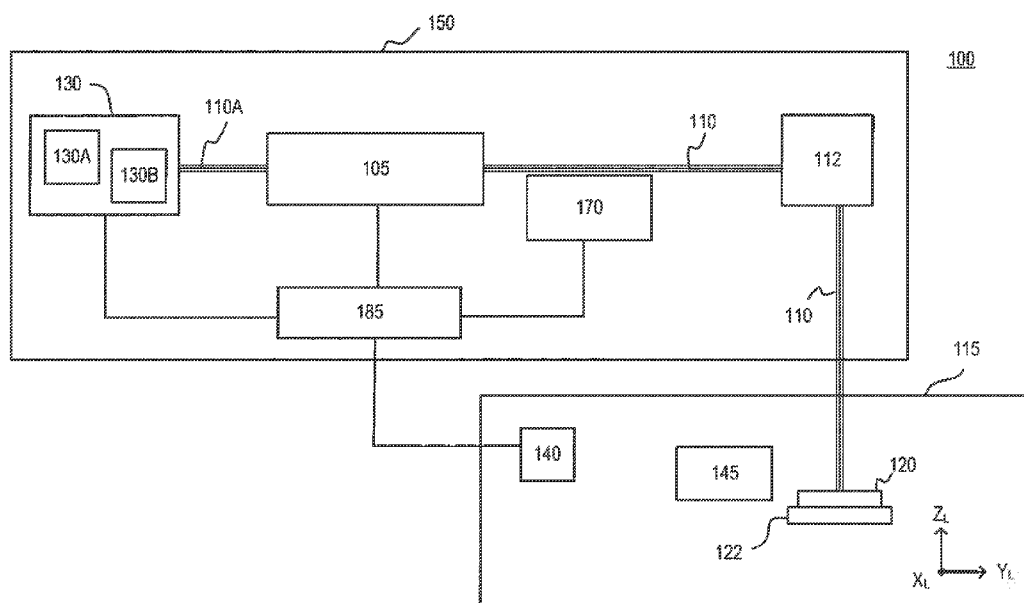


Fig. 1

(57) Abstract: A method includes producing a pulsed light beam; directing the pulsed light beam toward a substrate mounted to a stage of a lithography exposure apparatus; scanning a pulsed light beam and the substrate relative to each other, including projecting the pulsed light beam onto each sub-area of the substrate and moving one or more of the pulsed light beam and the substrate relative to each other; determining a value of a vibration of the stage for each sub-area of a substrate; for each sub-area of the substrate, determining an amount of adjustment to a bandwidth of die pulsed light beam, the adjustment amount compensating for a variation in the stage vibration so as to maintain a focus blur within a predetermined range of values across the substrate; and changing the bandwidth of the pulsed light beam by the determined adjustment amount to thereby compensate for the stage vibration variations.



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CONTROLLING FOR WAFER STAGE VIBRATION

CROSS REFERENCE TO RELATED APPLICATION

This application is related to U.S. Application No. 15/295,280, filed on October 17, 2016, which is incorporated herein by reference in its entirety.

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TECHNICAL FIELD

The disclosed subject matter relates to an apparatus for compensating for variations in the vibration of a wafer stage during scanning of the wafer by adjusting a characteristic of a pulsed light beam directed toward the wafer.

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BACKGROUND

In semiconductor lithography (or photolithography), the fabrication of an integrated circuit (IC) requires a variety of physical and chemical processes performed on a semiconductor (for example, silicon) substrate (which is also referred to as a wafer). A photolithography exposure apparatus or scanner is a machine that applies a desired pattern onto a target portion of the substrate. The wafer is fixed to a stage so that the wafer generally extends along a plane defined by orthogonal X_L and Y_L directions of the scanner. The wafer is irradiated by a light beam, which has a wavelength in the deep ultraviolet (DUV) range. The light beam travels along an axial direction, which corresponds with the Z_L direction of the scanner. The Z_L direction of the scanner is orthogonal to the lateral X_L - Y_L plane. The critical dimension (CD) is the smallest feature size of a pattern that can be printed on the wafer by the exposure apparatus. It is important to maintain a uniform or controlled CD to enable better control over the microelectronic features printed on the wafer.

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SUMMARY

In some general aspects, a method includes: producing, from the pulsed optical source, a pulsed light beam; directing the pulsed light beam toward a substrate mounted to a stage of a lithography exposure apparatus; performing a scanning operation between the pulsed light beam and the substrate, wherein the scanning operation comprises projecting the pulsed light beam onto each sub-area of the substrate and moving one or more of the pulsed light beam and the substrate relative to each other; determining a value of a vibration of the stage for each sub-area

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of a substrate; for each sub-area of the substrate, determining an amount of adjustment to a bandwidth of the pulsed light beam, the adjustment amount compensating for a variation in the stage vibration so as to maintain a focus blur within a predetermined range of values across the substrate; and changing the bandwidth of the pulsed light beam by the determined adjustment
5 amount as the pulsed light beam is exposing a substrate to thereby compensate for the stage vibration variations.

Implementations can include one or more of the following features. For example, the amount of adjustment to the bandwidth in a particular sub-area can be determined by accessing a lookup table to determine a value of the bandwidth that maintains an effective stage vibration
10 constant. The method can include creating the lookup table prior to directing the pulsed light beam toward the substrate.

The value of the stage vibration for each sub-area of a substrate can be determined by determining the value of the stage vibration for each sub-area of the substrate after a scanning operation has been performed between the pulsed light beam and the substrate. The bandwidth of
15 the pulsed light beam can be changed by the determined adjustment amount as the pulsed light beam is exposing a substrate by changing the bandwidth of the pulsed light beam by the determined adjustment amount as the pulsed light beam is exposing a substrate that has not yet been scanned by the pulsed light beam.

The amount of adjustment to the bandwidth of the pulsed light beam can be determined
20 prior to directing the pulsed light beam toward the substrate. The amount of adjustment to the bandwidth of the pulsed light beam can be determined while the pulsed light beam is directed toward the substrate and at each sub-area of the substrate.

The bandwidth of the pulsed light beam can be changed by adjusting one or more optical components of a spectral feature selection apparatus. The one or more optical components of the
25 spectral feature selection apparatus can be adjusted by rotating and translating a prism of the spectral feature selection apparatus.

The focus blur can be maintained within the predetermined range to maintain a critical dimension of a feature formed in the substrate to within a predetermined range.

The bandwidth of the pulsed light beam can be changed by changing the bandwidth in
30 between bursts of pulses of the pulsed light beam.

The method can include measuring a bandwidth of the pulsed light beam that is directed toward the substrate, and adjusting the bandwidth of the pulsed light beam if the measured bandwidth is outside an acceptable range of bandwidths.

In other general aspects, an apparatus includes: an optical source producing a pulsed light beam; a beam directing system directing the pulsed light beam toward a substrate mounted to a stage of a lithography exposure apparatus; a scanning system configured to project the pulsed light beam onto each sub-area of the substrate and move one or more of the pulsed light beam and the substrate relative to each other; a metrology apparatus configured to determine a value of a vibration of the stage for each sub-area of a substrate; and a control system connected to the optical source, the scanning system, and the metrology apparatus. The control system is configured to: receive the determined values of the stage vibration for each sub-area from the metrology apparatus; for each sub-area, determine an amount of adjustment to a bandwidth of the pulsed light beam, the adjustment amount compensating for a variation in the stage vibration so as to maintain a focus blur within a predetermined range of values across the substrate; and send a signal to the optical source to modify the bandwidth of the pulsed light beam by the determined adjustment amount as the pulsed light beam is exposing a substrate to thereby compensate for the stage vibration variation.

Implementations can include one or more of the following features. For example, scanning system can be configured to move one or more of the pulsed light beam and the substrate relative to each other along a lateral plane. The lateral plane is perpendicular to an axial direction along which the pulsed light beam is directed, and the metrology apparatus can be configured to determine the value of the vibration of the stage along the axial direction.

The apparatus can include a spectral feature selection apparatus configured to select a spectral feature of the pulsed light beam, the spectral feature selection apparatus including a set of optical components arranged in the path of the pulsed light beam, wherein the control system is connected to the spectral feature selection apparatus. The control system can send a signal to the optical source to modify the bandwidth of the pulsed light beam by sending a signal to the spectral feature selection apparatus to move at least one optical component to thereby change the bandwidth of the pulsed light beam. The set of optical components of the spectral feature selection apparatus can include at least one prism, and the control system can send the signal to the spectral feature selection apparatus to move the at least one optical component to thereby

change the bandwidth of the pulsed light beam by sending a signal to a rapid actuator associated with the at least one prism to cause the prism to rotate to thereby change the bandwidth.

The set of optical components of the spectral feature selection apparatus can include a dispersive optical element arranged to interact with the pulsed light beam, and a plurality of
5 prisms arranged in the path of the pulsed light beam between the dispersive optical element and the optical source.

The spectral feature selection apparatus can include an actuation system including at least one rapid actuator associated with a prism and configured to rotate the associated prism to thereby adjust a spectral feature of the pulsed light beam.

10 The rapid actuator can include a rotation stage that rotates about a rotation axis and includes a region that is mechanically linked to the prism. The rotation stage can be configured to rotate about the rotation axis along a full 360° of angle of rotation.

DESCRIPTION OF DRAWINGS

15 Fig. 1 is a block diagram of a photolithography system producing a pulsed light beam that is directed to a photolithography exposure apparatus;

Fig. 2 is a schematic drawing depicting a map of a wafer that is imaged within the photolithography exposure apparatus of Fig. 1, the map showing the sub-areas of the wafer;

Fig. 3 is a graph of an exemplary optical spectrum of the pulsed light beam produced by
20 the photolithography system of Fig. 1;

Fig. 4 is a block diagram of an exemplary photolithography exposure apparatus that can be used in the photolithography system of Fig. 1;

Fig. 5A is a block diagram of an exemplary spectral feature selection apparatus that can be used in the photolithography system of Fig. 1;

25 Fig. 5B is a block diagram of an exemplary prism within the spectral feature selection apparatus of Fig. 5A, and showing a beam magnification and beam refraction angle through the prism;

Fig. 6A is a block diagram of exemplary spectral feature selection apparatus that includes a rapid actuator associated with at least one of the prisms and can be used in the
30 photolithography system of Fig. 1;

Fig. 6B is a view taken along the 6B-6B section of one of the prisms of the apparatus of Fig. 6A;

Fig. 6C is a view along the Z_{SF} direction of the prism of Fig. 6B showing rotation of the prism;

Fig. 7A is a block diagram of exemplary spectral feature selection apparatus that includes a rapid actuator associated with at least one of the prisms and can be used in the photolithography system of Fig. 1;

Fig. 7B is a view taken along the 7B-7B section of one of the prisms of the apparatus of Fig. 7A;

Fig. 7C is a view along the Z_{SF} direction of the prism of Fig. 7B showing rotation of the prism;

Fig. 8 is a block diagram of an exemplary optical source that can be used in the photolithography system of Fig. 1;

Fig. 9 is a block diagram of an exemplary control system that can be used in the photolithography system of Fig. 1;

Fig. 10 is a flow chart of an exemplary procedure performed by the photolithography system of Fig. 1 to rapidly adjust a bandwidth of the pulsed light beam to compensate for a variation in stage vibration in each sub-area of the wafer;

Fig. 11 is a flow chart of an exemplary procedure performed by the photolithography system of Fig. 1 to determine an adjustment to the bandwidth of the pulsed light beam for each sub-area of the wafer; and

Fig. 12 are graphs of exemplary relationships between stage vibrations measured for all of the sub-areas of the wafer, and bandwidth of the pulsed light beam that compensate for unwanted variations in stage vibrations.

DESCRIPTION

Referring to Fig. 1, a photolithography system 100 includes an illumination system 150 that produces a pulsed light beam 110 having a wavelength that is nominally at a center wavelength and is directed to a photolithography exposure apparatus or scanner 115. The pulsed light beam 110 is used to pattern microelectronic features on a substrate or wafer 120 that is mounted to a stage 122 in the scanner 115. These microelectronic features patterned on the wafer

120 are limited in size by the critical dimension (CD), and the critical dimension is influenced by focus blur, which is a blur in the focus of the light beam 110 at the wafer 120. Focus blur is caused at least in part by the effects of chromatic aberration due to the bandwidth of the light beam 110, the stage vibration or oscillation along the Z_L direction, and a tilt of the stage 122
5 from the X_L - Y_L plane.

The stage vibration is the vibration of the stage 122 that happens along the Z_L direction. The stage vibration varies across the lateral direction (across the X_L and Y_L directions) of the wafer 120. For example, as shown in Fig. 2, an exemplary map 200 of a wafer 220 is shown in which the stage vibration along the Z_L direction is characterized by a moving standard deviation
10 (MSD) value that is derived from a stage interferometer error signal. Higher values of stage vibration blur the image and thus cause non-uniformity in the CD. The map 200 of the wafer 220 shows how the stage vibration varies across exposure fields 223 of the wafer 220. The exposure field 223 of the wafer 220 is the area of the wafer 220 that is exposed in one scan of an exposure slit or window.

15 Because the focus blur depends at least in part on the bandwidth of the light beam 110 and the stage vibration along the Z_L direction, it is possible to maintain the focus blur at a constant value by adjusting the bandwidth of the light beam as it is scanned across the wafer 220 to compensate for the variation in the stage vibration across the surface of the wafer 220. The photolithography system 100 and associated method described herein is designed to determine
20 the bandwidth adjustment or value at each location or sub-area (for example, each exposure field) of the wafer 220 that offsets the change in the focus blur otherwise caused by the variation in the stage vibration at that wafer sub-area to thereby maintain the focus blur and control the CD across the wafer 220. The adjustment to the bandwidth occurs while the light beam 110 is being scanned across the wafer 220. For example, under control of a spectral feature selection
25 apparatus 130, the bandwidth of the light beam 110 can be adjusted for each sub-area (such as each exposure field 223) of the wafer 220.

Moreover, in order to enable the rapid adjustment to the bandwidth for each sub-area of the wafer 120, 220, the spectral feature selection apparatus 130 has been redesigned to provide for more rapid adjustment of the bandwidth of the pulsed light beam 110 while the light beam
30 110 is being scanned across the wafer 120 to enable the adjustment of the bandwidth for each sub-area of the wafer 120.

Specifically, the spectral feature selection apparatus 130 can include a coarse spectral feature adjustment system 130A and a fine spectral feature adjustment system 130B. The coarse spectral feature adjustment system 130A is used for coarse, large range, and slow control of the spectral feature (such as the bandwidth), and is collection of optical components that interact with the pulsed light beam 110A produced by the optical source 104. The fine spectral feature adjustment system 130B is used for fine, narrow range, and fast control of the spectral feature such as the bandwidth. The fine spectral feature adjustment system 130B can include an optical system that interacts optically with the pulsed light beam 110A to control one or more spectral features. The fine bandwidth adjustment system 130C can include a non-optical system that interacts with other aspects of the optical source 105 in a rapid manner to control one or more spectral features such as the bandwidth. For example, the fine spectral feature adjustment system 130C can be configured to adjust aspects of the timing associated with the gas discharge chamber or chambers within the optical source 105 to thereby adjust the bandwidth of the pulsed light beam 110.

Details about the photolithography system 100 are described next. With reference again to Fig. 1, the illumination system 150 includes an optical source 105 that produces the pulsed light beam 110 at a pulse repetition rate that is capable of being changed. The illumination system 150 includes a control system 185 that communicates with the optical source 105 and other features within the illumination system 150. The illumination system 150 also communicates with the scanner 115 to control the operation of the illumination system 150 and aspects of the pulsed light beam 110.

The control system 185 is operatively connected to the pulsed optical source 105 and to the spectral feature selection apparatus 130. And, the scanner 115 includes a lithography controller 140 operatively connected to the control system 185 and components within the scanner 115.

The pulse repetition rate of the pulsed light beam 110 is the rate at which pulses of the light beam 110 are produced by the optical source 105. Thus, for example, the repetition rate of the pulsed light beam 110 is $1/\Delta t$, where Δt is the time between the pulses. The control system 185 is generally configured to control the repetition rate at which the pulsed light beam 110 is produced including modifying the repetition rate of the pulsed light beam as it is exposing the wafer 120 in the scanner 115.

In some implementations, the scanner 115 triggers the optical source 105 (through the communication between the controller 140 and the control system 185) to produce the pulsed light beam 110, so the scanner 115 controls the repetition rate, spectral features such as the bandwidth or wavelength, and/or the dose by way of the controller 140 and the control system 185. For example, the controller 140 sends a signal to the control system 185 to maintain the repetition rate of the light beam 110 within a particular range of acceptable rates. The scanner 115 generally maintains the repetition rate constant for each burst of pulses of the light beam 110. A burst of pulses of the light beam 110 can correspond to an exposure field on the wafer 120. The exposure field is the area of the wafer 120 that is exposed in one scan of an exposure slit or window within the scanner 115. A burst of pulses can include anywhere from 10 to 500 pulses, for example.

As discussed, the critical dimension (CD) is the smallest feature size that can be printed on the wafer 120 by the system 100. The CD depends on the wavelength of the light beam 110. Thus, in order to maintain a uniform CD of the microelectronic features printed on the wafer 120, and on other wafers exposed by the system 100, the center wavelength of the light beam 110 should remain at an expected or target center wavelength or within a range of wavelengths around the target wavelength. Thus, in addition to maintaining the center wavelength at the target center wavelength or within a range of acceptable wavelengths about the target center wavelength, it is desirable to maintain the bandwidth of the light beam 110 (the range of wavelengths in the light beam 110) to within an acceptable range of bandwidths.

In order to maintain the bandwidth of the light beam 110 to an acceptable range, or to adjust the bandwidth of the light beam 110, the control system 185 is configured to determine an amount of adjustment to the bandwidth of the pulsed light beam 110. Additionally, the control system 185 is configured to send a signal to the spectral feature selection apparatus 130 to move at least one optical component of the apparatus 130 (for example, the prism 520) to thereby change the bandwidth of the pulsed light beam 110 by the determined adjustment amount as the pulsed light beam 110 is exposing the wafer 120 to thereby compensate for the variation in stage vibration along the Z_L direction across the surface of the wafer 220.

In some implementations, the bandwidth of the pulsed light beam 110 can be changed in between any two bursts of pulses. In this example, the time that it takes for the bandwidth to be changed from a first value to a second value and also to stabilize at the second value should be

less than the time between the bursts of pulses. For example, if the period of time between bursts is 50 ms, then the total time to change the bandwidth from a first value to a second value and stabilize at the second value should be less than 50 ms. The time that it takes for the bandwidth to be changed from a first value to a second value and also to stabilize at the second value can be as low as 50 milliseconds (ms) in this example. In other implementations, it is possible to change the bandwidth of the pulsed light beam 110 during a burst of pulses or between exposure fields (and not necessarily between bursts). In some implementations, the bandwidth of the pulsed light beam 110 can be changed in between pulses of the light beam 110. For example, the bandwidth can be changed by 10 femtometers (fm) in about tens of microseconds (μ s), for example, within 100 to 200 μ s. In other implementations, the bandwidth of the pulsed light beam 110 is changed field to field (in between exposure fields); for example, the bandwidth can be changed by 100 fm in about 10 to 15 ms.

The control system 185 and the spectral feature selection apparatus 130 are designed to enable such a rapid change of the bandwidth, as discussed in detail below.

The controller 140 of the scanner 115 sends a signal to the control system 185 to adjust or modify an aspect (such as the bandwidth or the repetition rate) of the pulsed light beam 110 that is being scanned across the wafer 120. The signal sent to the control system 185 can cause the control system 185 to modify an electrical signal sent to the pulsed optical source 105 or an electrical signal sent to the apparatus 130. For example, if the pulsed optical source 105 includes a gas laser amplifier then the electrical signal provides a pulsed current to electrodes within one or more gas discharge chambers of the pulsed optical source 105.

The wafer 120 is placed on the wafer stage 122 (also referred to as a table) and the stage 122 is connected to a positioner configured to accurately position the wafer 120 in accordance with certain parameters and under control of the controller 140.

The photolithography system 100 can also include the measurement system 170, which can include a sub-system that measures one or more spectral features (such as the bandwidth or wavelength) of the light beam 110. Because of various disturbances applied to the photolithography system 100 during operation, the value of the spectral feature (such as the bandwidth or the wavelength) of the light beam 110 at the wafer 120 may not correspond to or match with the desired spectral feature (that is, the spectral feature that the scanner 115 expects). Thus, the spectral feature (such as a characteristic bandwidth) of light beam 110 is measured or

estimated during operation by estimating a value of a metric from the optical spectrum so that an operator or an automated system (for example, a feedback controller) can use the measured or estimated bandwidth to adjust the properties of the optical source 105 and to adjust the optical spectrum of the light beam 110. The sub-system of the measurement system 170 measures the spectral feature (such as the bandwidth and/or the wavelength) of the light beam 110 based on this optical spectrum.

The measurement system 170 receives a portion of the light beam 110 that is redirected from a beam separation device that is placed in a path between the optical source 105 and the scanner 115. The beam separation device directs a first portion or percentage of the light beam 110 into the measurement system 170 and directs a second portion or percentage of the light beam 110 toward the scanner 115. In some implementations, the majority of the light beam 110 is directed in the second portion toward the scanner 115. For example, the beam separation device directs a fraction (for example, 1-2%) of the light beam 110 into the measurement system 170. The beam separation device can be, for example, a beam splitter.

The pulses of the light beam 110 are centered around a wavelength that is in the deep ultraviolet (DUV) range, for example, with wavelengths of 248 nanometers (nm) or 193 nm. The size of the microelectronic features patterned on the wafer 120 depends, among other things, on the wavelength of the pulsed light beam 110, with a lower wavelength resulting in a small minimum feature size or critical dimension. When the wavelength of the pulsed light beam 110 is 248 nm or 193 nm, the minimum size of the microelectronic features can be, for example, 50 nm or less. The bandwidth that is used for analysis and control of the pulsed light beam 110 can be the actual, instantaneous bandwidth of its optical spectrum 300 (or emission spectrum), as shown in Fig. 3. The optical spectrum 300 contains information about how the optical energy or power of the light beam 110 is distributed over different wavelengths (or frequencies).

The light beam 110 is directed through a beam preparation system 112, which can include optical elements that modify aspects of the light beam 110. For example, the beam preparation system 112 can include reflective and/or refractive optical elements, optical pulse stretchers, and optical apertures (including automated shutters).

The illumination system 150 includes a spectral feature selection apparatus 130. The spectral feature selection apparatus 130 is placed at a first end of the optical source 105 to interact with a light beam 110A produced by the optical source 105. The light beam 110A is a

beam produced at one end of the resonators within the optical source 105 and can be a seed beam produced by a master oscillator, as discussed below. The spectral feature selection apparatus 130 is configured to finely tune the spectral properties of the pulsed light beam 110 by tuning or adjusting one or more spectral features (such as the bandwidth or wavelength) of the pulsed light beam 110A.

Referring also to Fig. 4, the wafer 120, 220 is irradiated by the light beam 110. The lithography exposure apparatus 115 includes an optical arrangement that includes an illuminator system 129 having, for example, one or more condenser lenses, a mask 134, and an objective arrangement 132. The mask 134 is movable along one or more directions, such as along a Z_L direction (which generally corresponds to the axial direction of the light beam 110) or in an X_L - Y_L plane that is perpendicular to the Z_L direction. The objective arrangement 132 includes a projection lens and enables the image transfer to occur from the mask 134 to the photoresist on the wafer 120. The illuminator system 129 adjusts the range of angles for the light beam 110 impinging on the mask 134. The illuminator system 129 also homogenizes (makes uniform) the intensity distribution of the light beam 110 across the mask 134.

The lithography apparatus 115 can include, among other features, a lithography controller 140, air conditioning devices, and power supplies for the various electrical components. The lithography controller 140 controls how layers are printed on the wafer 120.

In some implementations, an immersion medium can be supplied to cover the wafer 120. The immersion medium can be a liquid (such as water) for liquid immersion lithography. In other implementations in which the lithography is a dry system, the immersion medium can be a gas such as dry nitrogen, dry air, or clean air. In other implementations, the wafer 120 can be exposed within a pressure-controlled environment (such as a vacuum or partial vacuum).

Referring again to Fig. 4, a process program or recipe determines the length of the exposure on the wafer 120, the mask 134 used, as well as other factors that affect the exposure. During lithography, a plurality of pulses of the light beam 110 illuminate the same area of the wafer 120 to form an illumination dose. The number of pulses N of the light beam 110 that illuminate the same area can be referred to as an exposure window 400 and the size of the window 400 can be controlled by an exposure slit 405 placed before the mask 134. The slit 405 can be designed like a shutter and can include a plurality of blades that can be opened and closed. And, the size of the exposed area is determined by the distance between the blades in the

non-scanning direction and also by the length (distance) of the scan in the scanning direction. In some implementations, the value of N is in the tens, for example, from 10-100 pulses. In other implementations, the value of N is greater than 100 pulses, for example, from 100-500 pulses.

One or more of the wafer stage 122, the mask 134, and the objective arrangement 132 are fixed to associated actuation systems to thereby form a scanning arrangement. In the scanning arrangement, one or more of the mask 134, the objective arrangement 132, and the wafer 120 (via the stage 122) are moved relative to each other during the exposure to scan the exposure window 400 across an exposure field 223.

Referring again to Fig. 1, the photolithography system 100 also includes a wafer metrology apparatus 145 that is configured to determine a value of the stage vibration in the Z direction for each sub-area (for example, for each exposure field 223) of the wafer 120, 220. The metrology apparatus 145 is connected to the control system 185 so that the control system 185 receives the values of the stage vibration in the Z_L direction for each wafer sub-area. The control system 185 can store the values of the stage vibration in the Z_L direction for each wafer sub-area.

In some implementations, the metrology apparatus 145 is configured to be used in an offline mode in which the wafer 120, 220 is analyzed after or before the wafer 120, 220 has been patterned by the light beam 110. The data obtained by such a scan can be used by the control system 185 for one or more wafers that will be scanned in the future. The data obtained by such a scan can be used to create a correction map of the wafer 120, 220 that can be used for the next wafer to be scanned.

In other implementations, the metrology apparatus 145 is used in an online mode in which the wafer 120, 220 is analyzed while the wafer 120, 220 is being patterned by the light beam 110. For example, the exposure field of the wafer 120, 220 could be probed in between bursts of the light beam 110 or another aspect of the scanner 115 that indicates the stage vibration in the Z_L direction can be probed during scanning of the wafer 120, 220.

The metrology apparatus 145 can be any apparatus that can probe the stage vibrations. In some implementations, the metrology apparatus 145 includes an interferometer that measures small displacements or and surface irregularities on the surface of the wafer 120 at each wafer sub-area (such as each wafer exposure field 223). From this data, a moving standard deviation (MSD) value along the Z_L direction at each wafer sub-area (such as each wafer exposure field

223) can be derived and the value of the MSD_{Z_L} can be considered to represent the stage vibration along the Z_L direction.

As another example, the metrology apparatus 145 can be the scanner 115, which can perform probe the wafer 120 before exposure or between scans of the wafer 120.

5 The metrology apparatus 145 can be a self-contained system such as a high resolution scanning electron microscope (SEM) that is designed for high resolution imaging, to be able to display feature sizes of less than, for example 1 nm. The SEM is a type of electron microscope that produces images of a sample (in this case, the wafer 120) by scanning the wafer 120 with a focused beam of electrons. The SEM can achieve resolution better than 1 nanometer (nm).

10 The metrology apparatus 145 can employs scanning white light interferometry, which provides quantitative noncontact, three dimensional measurements of the wafer 120. In this technique, a white light beam passes through a filter and then a microscope objective lens to the surface of the wafer 120. The light reflecting back from the surface of the wafer 120 is combined with a reference beam and captured for software analysis within the apparatus 145. After
15 obtaining data for each point, the apparatus 145 can generate a three dimensional image (topography) of the surface of the wafer 120. Such a topographical map of the wafer 120 enables the measurement of stage vibration.

In other implementations, the metrology apparatus 145 is a scatterometer that transmits a pulse of energy toward the wafer 120 and measures the reflected or diffracted energy from the
20 wafer 120.

Referring to Fig. 5A, in some implementations, the spectral feature selection apparatus 130 includes a set of optical features or components 500, 505, 510, 515, 520 arranged to optically interact with the pulsed light beam 110A and a control module 550 that includes electronics in the form of any combination of firmware and software. The optical components
25 500, 505, 510, 515, 520 can be configured to provide a coarse spectral feature adjustment system 130A (shown in Fig. 1); and, if the adjustment of such components is rapid enough, it can be configured to provide a fine spectral feature adjustment system 130B (shown in Fig. 1). Although not shown in Fig. 5A, it is possible for the spectral feature selection apparatus 130 to include other optical features or other non-optical features for providing fine spectral feature
30 control.

The control module 550 is connected to one or more actuation systems 500A, 505A, 510A, 515A, 520A physically coupled to respective optical components 500, 505, 510, 515, 520. The optical components of the apparatus 130 include a dispersive optical element 500, which can be a grating, and a beam expander 501 made of a set of refractive optical elements 505, 510, 515, 520, which can be prisms. The grating 500 can be a reflective grating that is designed to disperse and reflect the light beam 110A; accordingly, the grating 500 is made of a material that is suitable for interacting with a pulsed light beam 110A having a wavelength in the DUV range. Each of the prisms 505, 510, 515, 520 is a transmissive prism that acts to disperse and redirect the light beam 110A as it passes through the body of the prism. Each of the prisms can be made of a material (such as, for example, calcium fluoride) that permits the transmission of the wavelength of the light beam 110A.

The prism 520 is positioned farthest from the grating 500 while the prism 505 is positioned closest to the grating 500. The pulsed light beam 110A enters the apparatus 130 through an aperture 555, and then travels through the prism 520, the prism 510, and the prism 505, in that order, prior to impinging upon a diffractive surface 502 of the grating 500. With each passing of the beam 110A through a consecutive prism 520, 515, 510, 505, the light beam 110A is optically magnified and redirected (refracted at an angle) toward the next optical component. The light beam 110A is diffracted and reflected from the grating 500 back through the prism 505, the prism 510, the prism 515, and the prism 520, in that order, prior to passing through the aperture 555 as the light beam 110A exits the apparatus 130. With each passing through the consecutive prisms 505, 510, 515, 520 from the grating 300, the light beam 110A is optically compressed as it travels toward the aperture 555.

Referring to Fig. 5B, the rotation of a prism P (which can be any one of prisms 505, 510, 515, or 520) of the beam expander 501 changes an angle of incidence at which the light beam 110A impinges upon the entrance surface $H(P)$ of that rotated prism P. Moreover, two local optical qualities, namely, an optical magnification $OM(P)$ and a beam refraction angle $\delta(P)$, of the light beam 110A through that rotated prism P are functions of the angle of incidence of the light beam 110A impinging upon the entrance surface $H(P)$ of that rotated prism P. The optical magnification $OM(P)$ of the light beam 110A through the prism P is the ratio of a transverse wide $Wo(P)$ of the light beam 110A exiting that prism P to a transverse width $Wi(P)$ of the light beam 110A entering that prism P.

A change in the local optical magnification $OM(P)$ of the light beam 110A at one or more of the prisms P within the beam expander 501 causes an overall change in the optical magnification OM 565 of the light beam 110A through the beam expander 501. The optical magnification OM 565 of the light beam 110A through the beam expander 501 is the ratio of the transverse width W_o of the light beam 110A exiting the beam expander 501 to a transverse width W_i of the light beam 110A entering the beam expander 501.

Additionally, a change in the local beam refraction angle $\delta(P)$ through one or more of the prisms P within the beam expander 501 causes an overall change in an angle of incidence of 562 of the light beam 110A at the surface 502 of the grating 500.

The wavelength of the light beam 110A can be adjusted by changing the angle of incidence 562 at which the light beam 110A impinges upon the diffractive surface 502 of the grating 500. The bandwidth of the light beam 110A can be adjusted by changing the optical magnification 565 of the light beam 110.

The spectral feature selection apparatus 130 is redesigned to provide for more rapid adjustment of the bandwidth of the pulsed light beam 110 while the light beam 110 is being scanned across the wafer 120 by the scanner 115. The spectral feature selection apparatus 130 can be redesigned with one or more new actuation systems for more effectively and more rapidly rotating one or more of the optical components 500, 505, 510, 515, 520.

For example, the spectral feature selection apparatus 130 includes a new actuation system 520A for more effectively and more rapidly rotating the prism 520. The new actuation system 520A can be designed in a manner that increases the speed with which the prism 520 is rotated. Specifically, the axis of rotation of the prism 520 mounted to the new actuation system 520A is parallel with a rotatable motor shaft 522A of the new actuation system 520A. In other implementations, the new actuation system 520A can be designed to include an arm that is physically linked to the motor shaft 522A at one end and physically linked to the prism 520 at the other end to provide additional leverage for rotating the prism 520. In this way, the optical magnification OM of the light beam 110A is made to be more sensitive to rotation of the prism 520.

In some implementations, the prism 505 is flipped relative to the prior design of the beam expander to provide for more rapid adjustment of the bandwidth. In these cases, the bandwidth change becomes relatively faster (when compared with prior designs of the apparatus 130) with a

relatively smaller rotation of the prism 520. The change in optical magnification per unit rotation of the prism 520 is increased in the redesigned spectral feature selection apparatus 130 when compared with prior spectral feature selection apparatuses.

The apparatus 130 is designed to adjust the wavelength of the light beam 110A that is produced within the resonator or resonators of the optical source 105 by adjusting an angle 562 of incidence of at which the light beam 110A impinges upon the diffractive surface 502 of the grating 500. Specifically, this can be done by rotating one or more of the prisms 505, 510, 515, 520 and the grating 500 to thereby adjust the angle of incidence 562 of the light beam 110A.

Moreover, the bandwidth of the light beam 110A that is produced by the optical source 105 is adjusted by adjusting the optical magnification OM 565 of the light beam 110A. Thus, the bandwidth of the light beam 110A can be adjusted by rotating one or more of the prisms 505, 510, 515, 520, which causes the optical magnification 565 of the light beam 110A to change.

Because the rotation of a particular prism P causes a change in both the local beam refraction angle $\delta(P)$ and the local optical magnification OM(P) at that prism P, the control of wavelength and bandwidth are coupled in this design.

Additionally, the bandwidth of the light beam 110A is relatively sensitive to the rotation of the prism 520 and relatively insensitive to rotation of the prism 505. This is because any change in the local optical magnification OM(520) of the light beam 110A due to the rotation of the prism 520 is multiplied by the product of the change in the optical magnification OM(515), OM(510), OM(505), respectively, in the other prisms 515, 510, and 505 because those prisms are between the rotated prism 520 and the grating 500, and the light beam 110A must travel through these other prisms 515, 510, 505 after passing through the prism 520. On the other hand, the wavelength of the light beam 110A is relatively sensitive to the rotation of the prism 505 and relatively insensitive to the rotation of the prism 520.

For example, in order to change the bandwidth without changing the wavelength, the optical magnification 565 should be changed without changing the angle of incidence 562, and this can be achieved by rotating the prism 520 by a large amount and rotating the prism 505 by a small amount.

The control module 550 is connected to one or more actuation systems 500A, 505A, 510A, 515A, 520A that are physically coupled to respective optical components 500, 505, 510, 515, 520. Although an actuation system is shown for each of the optical components it is

possible that some of the optical components in the apparatus 130 are either kept stationary or are not physically coupled to an actuation system. For example, in some implementations, the grating 500 can be kept stationary and the prism 515 can be kept stationary and not physically coupled to an actuation system.

5 Each of the actuation systems 500A, 505A, 510A, 515A, 520A includes one or more actuators that are connected to their respective optical components. The adjustment of the optical components causes the adjustment in the particular spectral features (the wavelength and/or bandwidth) of the light beam 110A. The control module 550 receives a control signal from the control system 185, the control signal including specific commands to operate or control one or
10 more of the actuation systems. The actuation systems can be selected and designed to work cooperatively.

Each of the actuators of the actuation systems 500A, 505A, 510A, 515A, 520A is a mechanical device for moving or controlling the respective optical component. The actuators receive energy from the module 550, and convert that energy into some kind of motion imparted
15 to the respective optical component. For example, the actuation systems can be any one of force devices and rotation stages for rotating one or more of prisms of a beam expander. The actuation systems can include, for example, motors such as stepper motors, valves, pressure-controlled devices, piezoelectric devices, linear motors, hydraulic actuators, voice coils, etc.

The grating 500 can be a high blaze angle Echelle grating, and the light beam 110A
20 incident on the grating 500 at any angle of incidence 562 that satisfies a grating equation will be reflected (diffracted). The grating equation provides the relationship between the spectral order of the grating 500, the diffracted wavelength (the wavelength of the diffracted beam), the angle of incidence 562 of the light beam 110A onto the grating 500, the angle of exit of the light beam 110A diffracted off the grating 500, the vertical divergence of the light beam 110A incident onto
25 the grating 500, and the groove spacing of the diffractive surface of the grating 500. Moreover, if the grating 500 is used such that the angle of incidence 562 of the light beam 110A onto the grating 500 is equal to the angle of exit of the light beam 110A from the grating 500, then the grating 500 and the beam expander (the prisms 505, 510, 515, 520) are arranged in a Littrow configuration and the wavelength of the light beam 110A reflected from the grating 500 is the
30 Littrow wavelength. It can be assumed that the vertical divergence of the light beam 110A incident onto the grating 500 is near zero. To reflect the nominal wavelength, the grating 500 is

aligned, with respect to the light beam 110A incident onto the grating 500, so that the nominal wavelength is reflected back through the beam expander (the prisms 505, 510, 515, 520) to be amplified in the optical source 105. The Littrow wavelength can then be tuned over the entire gain bandwidth of the resonators within optical source 105 by varying the angle of incidence 562 of the light beam 110A onto the grating 500.

Each of the prisms 505, 510, 515, 520 is wide enough along the transverse direction of the light beam 110A so that the light beam 110A is contained within the surface at which it passes. Each prism optically magnifies the light beam 110A on the path toward the grating 500 from the aperture 555, and therefore each prism is successively larger in size from the prism 520 to the prism 505. Thus, the prism 505 is larger than the prism 510, which is larger than the prism 515, and the prism 520 is the smallest prism.

The prism 520 that is the farthest from the grating 500, and is also the smallest in size, is mounted on the actuation system 520A, and specifically to the rotation shaft 522A, which causes the prism 520 to rotate, and such rotation changes the optical magnification of the light beam 110A impinging upon the grating 500 to thereby modify the bandwidth of the light beam 110A output from the apparatus 130. The actuation system 520A is designed as a rapid actuation system 520A because it includes a rotary stepper motor that includes the rotation shaft 522A to which the prism 520 is fixed. The rotation shaft 522A rotates about its shaft axis, which is parallel with the rotation axis of the prism 520. Moreover, because the actuation system 520A includes the rotary stepper motor, it lacks any mechanical memory and also lacks an energy ground state. Each location of the rotation shaft 522A is at the same energy as each of the other locations of the rotation shaft 522A and the rotation shaft 522A lacks a preferred resting location with a low potential energy.

Referring to Figs. 6A and 6B, in a first implementation, a spectral feature selection apparatus 630 is designed with a grating 600 and four prisms 605, 610, 615, 620. The grating 600 and the four prisms 605, 610, 615, 620 are configured to interact with the light beam 110A produced by the optical source 105 after the light beam 110A passes through an aperture 655 of the apparatus 630. The light beam 110A travels along a path in an X_{SF} - Y_{SF} plane of the apparatus 630 from the aperture 655, through the prism 620, the prism 615, the prism 610, the prism 605, and then is reflected from the grating 600, and back through the prisms 605, 610, 615, 620 before exiting the apparatus through the aperture 655.

The prisms 605, 610, 615, 620 are right-angled prisms through which the pulsed light beam 110A is transmitted so that the pulsed light beam 110A changes its optical magnification as it passes through each right-angled prism. The right-angled prism 620 that is farthest from the dispersive optical element 600 has the smallest hypotenuse of the plurality, and each consecutive
 5 right-angled prism closer to the dispersive optical element 600 has a larger or same size hypotenuse than the adjacent right-angled prism that is farther from the dispersive optical element.

For example, the prism 605 that is closest to the grating 600 is also the largest in size, for example, its hypotenuse has the largest extent of the four prisms 605, 610, 615, 620. The prism
 10 620 that is farthest from the grating 600 is also the smallest in size, for example, its hypotenuse has the smallest extent of the four prisms 605, 610, 615, 620. It is possible for adjacent prisms to be the same size. But, each prism that is closer to the grating 600 should be at least as large or greater than in size its adjacent prism because the light beam 110A is optically magnified as travels through the prism 620, the prism 615, the prism 610, and the prism 605, and thus the
 15 transverse extent of the light beam 110A enlarges as the light beam 110A gets closer to the grating 600. The transverse extent of the light beam 110A is the extent along the plane that is perpendicular to the propagation direction of the light beam 110A. And, the propagation direction of the light beam 110A is in the X_{SF} - Y_{SF} plane of the apparatus 630.

The prism 605 is physically coupled to an actuation system 605A that rotates the prism
 20 605 about an axis that is parallel with the Z_{SF} axis of the apparatus 630, the prism 610 is physically coupled to an actuation system 610A that rotates the prism 610 about an axis that is parallel with the Z_{SF} axis, and the prism 620 is physically coupled to a rapid actuation system 620A. The rapid actuation system 620A is configured to rotate the prism 605 about an axis that is parallel with the Z_{SF} axis of the apparatus 630.

The rapid actuation system 620A includes a rotary stepper motor 621A that has a rotation
 25 shaft 622A and rotation plate 623A fixed to the rotation shaft 622A. The rotation shaft 622A and therefore the rotation plate 623A rotate about a shaft axis AR that is parallel with a center of mass (that corresponds to a rotation axis AP) of the prism 620 and is also parallel with the Z_{SF} axis of the apparatus 630. Although not necessary, the shaft axis AR of the prism 620 can
 30 correspond with or align with the center of mass (the rotation axis AP) of the prism 620 along the X_{SF} - Y_{SF} plane. In some implementations, the center of mass (or rotation axis AP) of the prism

620 is offset from the shaft axis AR along the X_{SF} - Y_{SF} plane. By offsetting the shaft axis AR from the prism 620 center of mass, the position of the light beam 110A can be adjusted to be at a particular position on the surface of the grating 600 whenever the prism 620 is rotated.

By mounting the prism 620 to the rotation plate 623A, the prism 620 is directly rotated
5 about its rotation axis AP as the shaft 622A and rotation plate 623A are rotated about their shaft axis AR. In this way, rapid rotation or control of the prism 620 is enabled when compared with a system that uses a linear stepper motor having a linearly translatable shaft (that is converted into a rotational motion using a flexure). Because a rotational step of the shaft 622A (and plate 623A) directly correlates to a rotational step of the prism 620 (without the imparting any a linear
10 motion), the rotary stepper motor 621A is able to rotate the prism 620 at a speed that enables more rapid adjustment of spectral features (such as the bandwidth) of the light beam 110A and therefore the light beam 110. The rotary design of the stepper motor 621A imparts a purely rotational motion to the prism 620, which is mounted without the use of any linear motion or flexure motion that are found on prior actuators for the prism 620. Moreover, the use of a rotary
15 shaft 622A enables the prism 620 to be rotated about a full 360° , unlike the prior actuator that used a linear stepper motor plus a flexure design (in which the prism 620 could only be rotated about the angle determined from the flexure). In some implementations, in order to achieve a tuning of the bandwidth of the light beam 110A in an acceptable range, the prism 620 is capable of being rotated by 15 degrees. The prism 620 can be rotated by larger than 15 degrees though it
20 is not necessary with the current bandwidth range requirements.

In some implementations, the stepper motor 621A can be a direct drive stepper motor. A direct drive stepper motor is a conventional electromagnetic motor that uses a built-in step motor functionality for position control. In other implementations in which a higher resolution in motion may be needed, the stepper motor 621A can use a piezoelectric motor technology.

25 The stepper motor 621A can be a rotary stage that is controlled with a motor controller using a variable-frequency drive control method to provide the rapid rotation of the prism 620.

As discussed above, the advantage of using a rotary stepper motor 621A is to obtain more rapid rotation of the prism 620 because the rotation axis AP of the prism 620 is parallel with the rotational shaft 622A and also the shaft axis AR. Thus, for every unit rotation of the shaft 622A,
30 the prism 620 rotates by an incremental unit and the prism 620 rotates as fast as the rotational shaft 622A can rotate. In some implementations, in order to increase the stability of this

configuration, and increase the stability of the prism 620, the rapid actuation system 620A includes a position monitor 624A that is configured to detect a position of the rotational shaft 622A of the rotary stepper motor 621A. The error between the measured position of the rotational shaft 622A and the expected or target position of the rotational shaft 622A correlates
5 directly with the error in the position of the prism 620 and thus, this measurement can be used to determine the rotational error of the prism 620 (that is, the difference between actual rotation and commanded rotation) and to correct for this error during operation.

The control module 550 is connected to the position monitor 624A to receive the value of the position of the rotational shaft 622A and the control module 550 is also able to access a
10 stored or current value of the commanded position of the rotational shaft 622A so that the control module 550 can perform the calculation to determine the difference between the measured value of the position and the commanded position of the rotational shaft 622A and also determine how to adjust the rotational shaft 622A to reduce this error. For example, the control module 550 can determine a size of rotation as well as a direction of rotation of the rotational shaft 622A to offset
15 the error. Alternatively, it is possible for the control system 185 to perform this analysis.

The position monitor 624A can be a very high resolution optical rotary encoder that is built integrally with the rotational plate 623A. The optical rotary encoder uses optical sensing technology and on the rotation of an internal code disc that has opaque lines and patterns on it. For example, the plate 623A is rotated (hence the name rotary encoder) in a beam of light such
20 as a light emitting diode and the markings on the plate 623A act as shutters blocking and unblocking the light. An internal photodiode detector senses the alternating light beam and the encoder's electronics convert the pattern into an electrical signal that is then passed on to the control module 550 through the output of the encoder 624A.

In some implementations, the control module 550 can be designed with a rapid internal
25 dedicated controller solely for operating the rotary stepper motor 621A. For example, the rapid internal dedicated controller can receive the high resolution position data from the encoder 624A and can send a signal directly to the rotary stepper motor 621A to adjust the position of the shaft 622A and thereby adjust the position of the prism 620.

Referring also to Fig. 6C, the illumination system 150 changes a spectral feature such as
30 the bandwidth of the light beam 110A under control of the control system 185, which interfaces with the control module 550. For example, in order to coarsely and broadly control the

bandwidth of the light beam 110A and the light beam 110, the control module 550 sends a signal to the rotary stepper motor 621A of the rapid actuation system 620A to rotate the rotational shaft 622A from a first angle θ_1 (on the left side of Fig. 6C) to a second angle θ_2 (where $\Delta\theta = \theta_2 - \theta_1$) (on the right side of Fig. 6C). And, this change of angle of the shaft 622A is directly
5 imparted to the plate 623A, which is fixed to the shaft 622A, and thereby also imparted to the prism 620, which is fixed to the plate 623A. The rotation of the prism 620 from θ_1 to θ_2 causes a corresponding change in the optical magnification OM 565 of the pulsed light beam 110A that interacts with the grating 600 from OM1 to OM2, and the change in the optical magnification 565 of the pulsed light beam 110A causes a change in the bandwidth of the pulsed light beam
10 110A (and the light beam 110 as well). The range of the bandwidth that can be achieved by rotating the prism 620 using this rapid actuation system 620A can be a broad range and can be from about 100 femtometers (fm) to about 450 fm. The overall bandwidth range achievable can be at least 250 fm.

The rotation of the prism 620 associated with the rapid actuation system 620A by one
15 unit of rotation of the rotational shaft 622A causes the bandwidth of the pulsed light beam 110A to change by an amount that is less than a resolution of a bandwidth measurement device (for example, as a part of the measurement system 170, which is discussed below) that measures the bandwidth of the pulsed light beam 110. The prism 620 can be rotated by up to 15 degrees to achieve such a change in bandwidth. In practice, the amount of rotation of the prism 620 is
20 constrained only by the optical layout of the other components of the apparatus 630. For example, a rotation that is too large could cause the light beam 110A to be displaced by an amount that is so large that the light beam 110A does not impinge upon the next prism 615. In some implementations, in order to achieve a tuning of the bandwidth of the light beam 110A in an acceptable range, the prism 620 is capable of being rotated by 15 degrees, without risk of the
25 light beam 110A walking off any of the other prisms 605, 610, or 615. The prism 620 can be rotated by larger than 15 degrees though it is not necessary with the current bandwidth range requirements.

Referring again to Fig. 6A, the prism 610 can be mounted to an actuation system 610A that causes the prism 410 to rotate, and such rotation of the prism 610 can provide for fine
30 control of the wavelength of the light beam 110A. The actuation system 610A can include a rotary stepper motor that is controlled with a piezoelectric motor. The piezoelectric motor

operates by making use of the converse piezoelectric effect in which a material produces acoustic or ultrasonic vibrations in order to produce a linear or rotary motion.

The next prism 615 that is closer to the grating 600, and has a size that is either larger than or equal to the size of the prism 620, can be fixed in space in some implementations. The
5 next prism 610 that is closer to the grating 600 has a size that is either larger than or equal to the size of the prism 615.

The prism 605 that is closest to the grating 610 has a size that is either larger than or equal to the size of the prism 610 (the prism 605 is the largest prism of the beam expander). The prism 605 can be mounted to an actuation system 605A that causes the prism 605 to rotate and
10 such rotation of the prism 605 can provide for coarse control of the wavelength of the light beam 110A. For example, the prism 605 can be rotated by 1-2 degrees to tune the wavelength of the light beam 110A (and thus the light beam 110) from about 193.2 nanometers (nm) to about 193.5 nm. In some implementations, the actuation system 605A includes a rotary stepper motor that includes a mounting surface (such as the plate 623A) to which the prism 605 is fixed and a motor
15 shaft that rotates the mounting surface. The motor of the actuation system 605A can be a piezoelectric motor that is fifty times faster than a prior linear stepper motor and flexure combination design. Like the actuation system 620A, the actuation system 605A can include an optical rotary encoder that provides angular position feedback for the control system 185 or the control module 650.

Referring to Figs. 7A and 7B, in another implementation of the spectral feature selection
20 apparatus 730, a rapid actuation system 720A is designed to rotate the prism 720 of a beam expander that is farthest from the grating 700 about the shaft axis AR. Optionally or additionally, the actuation system 710A associated with the prism 710 can also be a rapid actuation system that is designed like the rapid actuation system 720A or 620A.

The apparatus 730 includes an extending arm 725A that has a first region 740A that is
25 mechanically linked to the rotational plate 723A at the location of the shaft axis AR. The extending arm 725A has a second region 745A that is offset from the shaft axis AR along a direction in the X_{SF} - Y_{SF} plane (and thus along a direction that is perpendicular to the shaft axis AR) so that the second region 745A is not intersected by the shaft axis AR. The prism 720 is
30 mechanically linked to the second region 745A.

Both the center of mass (the prism axis AP) of the prism 720 and the shaft axis AR remain parallel with the Z_{SF} axis of the apparatus 730; however, the center of mass of the prism 720 is offset from the shaft axis AR. A rotation of the extending arm 725A about the shaft axis AR by an angle $\Delta\theta$ imparts a combined movement to the prism 720: a rotation R of the prism
 5 720 about the shaft axis AR by an angle $\Delta\theta$ (see Fig. 5C) within the X_{SF} - Y_{SF} plane, and a linear translation T to the prism 720 along a direction that lies within the X_{SF} - Y_{SF} plane of the apparatus 730. In the example of Fig. 7C, the prism 720 is rotated R from a first angle θ_1 to a second angle θ_2 and is translated T from a first position Pos1 in the X_{SF} - Y_{SF} plane to a second position Pos2 in the X_{SF} - Y_{SF} plane.

10 The linear translation T to the prism 720 thereby translates the light beam 110A along a direction that is parallel with the longer axis 701 of the surface 702 of the grating 700. The longer axis 701 also lies along the X_{SF} - Y_{SF} plane of the apparatus 730. By performing this translation of the light beam 110A, it is possible to control which area or region of the grating 700 is illuminated at the lower end of the range of possible optical magnifications OM.

15 Moreover, the grating 700 and the surface 702 of the grating is non-uniform; namely, some regions of the surface 702 of the grating 700 impart a different change to the wavefront of the light beam 110A than other regions of the surface 702 of the grating 700 and some regions of the surface 702 impart more distortion to the wavefront of the light beam 110A than other regions of the surface 702. The control system 185 (or control module 550) can control the rapid actuation
 20 system 720A to thereby adjust the linear translation T to the prism 720 and adjust the translation of the light beam 110A along the longer axis 701 to take advantage of the non-uniformity of the grating 700 surface 702 and illuminate a higher distortion region of the grating surface 702 near one end of the grating surface 702 to raise the spectral bandwidth even more than the effect of simply lowering the optical magnification would achieve.

25 Additionally, the linear translation T to the prism 720 also translates the hypotenuse H (see Fig. 7C) of the prism 720 during rotation of the prism 720 relative to the location of the light beam 110A. The translation to the hypotenuse H therefore exposes new regions of the hypotenuse H to the light beam 110A during operation of the apparatus 730. Over the lifetime of the apparatus 730, the prism 720 is rotated from one end of its rotation range to the other end and
 30 also more regions are exposed to the light beam 110A, which reduces the amount of damage imparted to the prism 720 by the light beam 110A.

Similar to the apparatus 630, the spectral feature selection apparatus 730 also includes a grating 600, and the beam expander includes the prisms 705, 710, 715, which are positioned along the path of the light beam 110A between the prism 720 and the grating 700. The grating 700 and the four prisms 705, 710, 715, 720 are configured to interact with the light beam 110A produced by the optical source 105 after the light beam 110A passes through an aperture 755 of the apparatus 730. The light beam 110A travels along a path in the X_{SF} - Y_{SF} plane of the apparatus 730 from the aperture 755, through the prism 720, the prism 715, the prism 710, the prism 705, and then is reflected from the grating 700, and back through the consecutive prisms 705, 710, 715, 720 before exiting the apparatus 730 through the aperture 755.

Referring to Fig. 8, an exemplary optical source 805 is a pulsed laser source that produces a pulsed laser beam as the light beam 110. The optical source 805 is a two-stage laser system that includes a master oscillator (MO) 800 that provides the seed light beam 110A to a power amplifier (PA) 810. The master oscillator 800 typically includes a gain medium in which amplification occurs and an optical feedback mechanism such as an optical resonator. The power amplifier 810 typically includes a gain medium in which amplification occurs when seeded with the seed laser beam from the master oscillator 800. If the power amplifier 810 is designed as a regenerative ring resonator then it is described as a power ring amplifier (PRA) and in this case, enough optical feedback can be provided from the ring design. The spectral feature selection apparatus 130 receives the light beam 110A from the master oscillator 800 to enable fine tuning of spectral parameters such as the center wavelength and the bandwidth of the light beam 110A at relatively low output pulse energies. The power amplifier 810 receives the light beam 110A from the master oscillator 800 and amplifies this output to attain the necessary power for output to use in photolithography.

The master oscillator 800 includes a discharge chamber having two elongated electrodes, a laser gas that serves as the gain medium, and a fan circulating the gas between the electrodes. A laser resonator is formed between the spectral feature selection apparatus 130 on one side of the discharge chamber, and an output coupler 815 on a second side of the discharge chamber to output the seed light beam 110A to the power amplifier 810.

The optical source 805 can also include a line center analysis module (LAM) 820 that receives an output from the output coupler 815, and one or more beam modification optical systems 825 that modify the size and/or shape of the beam as needed. The line center analysis

module 820 is an example of one type of measurement system within the measurement system 170 that can be used to measure the wavelength (for example, the center wavelength) of the seed light beam.

5 The power amplifier 810 includes a power amplifier discharge chamber, and if it is a regenerative ring amplifier, the power amplifier also includes a beam reflector or beam turning device 830 that reflects the light beam back into the discharge chamber to form a circulating path. The power amplifier discharge chamber includes a pair of elongated electrodes, a laser gas that serves as the gain medium, and a fan for circulating the gas between the electrodes. The seed light beam 110A is amplified by repeatedly passing through the power amplifier 810. The beam
10 modification optical system 825 provides a way (for example, a partially-reflecting mirror) to in-couple the seed light beam 110A and to out-couple a portion of the amplified radiation from the power amplifier to form the output light beam 110.

The laser gas used in the discharge chambers of the master oscillator 800 and the power amplifier 810 can be any suitable gas for producing a laser beam around the required
15 wavelengths and bandwidth. For example, the laser gas can be argon fluoride (ArF), which emits light at a wavelength of about 193 nm, or krypton fluoride (KrF), which emits light at a wavelength of about 248 nm.

The line center analysis module 820 monitors the wavelength of the output (the light beam 110A) of the master oscillator 800. The line center analysis module 820 can be placed at
20 other locations within the optical source 805, or it can be placed at the output of the optical source 805.

Referring to Fig. 9, details about the control system 185 are provided that relate to the aspects of the system and method described herein. The control system 185 can include other features not shown in Fig. 9. In general, the control system 185 includes one or more of digital
25 electronic circuitry, computer hardware, firmware, and software.

The control system 185 includes memory 900, which can be read-only memory and/or random access memory. Storage devices suitable for tangibly embodying computer program instructions and data include all forms of non-volatile memory, including, by way of example, semiconductor memory devices, such as EPROM, EEPROM, and flash memory devices;
30 magnetic disks such as internal hard disks and removable disks; magneto-optical disks; and CD-ROM disks. The control system 185 can also include one or more input devices 905 (such as a

keyboard, touch screen, microphone, mouse, hand-held input device, etc.) and one or more output devices 910 (such as a speaker or a monitor).

The control system 185 includes one or more programmable processors 915, and one or more computer program products 920 tangibly embodied in a machine-readable storage device
5 for execution by a programmable processor (such as the processors 915). The one or more programmable processors 915 can each execute a program of instructions to perform desired functions by operating on input data and generating appropriate output. Generally, the processor 915 receives instructions and data from memory 900. Any of the foregoing may be supplemented by, or incorporated in, specially designed ASICs (application-specific integrated circuits).

10 The control system 185 includes, among other components, a spectral feature analysis module 925, a metrology module 927, a lithography analysis module 930, a decision module 935, a light source actuation module 950, a lithography actuation module 955, and a beam preparation actuation module 960. Each of these modules can be a set of computer program products executed by one or more processors such as the processors 915. Moreover, any of the
15 modules 925, 930, 935, 950, 955, 960 can access data stored within the memory 900.

The spectral feature analysis module 925 receives the output from the measurement system 170. The metrology module 927 receives the data from the metrology apparatus 145. The lithography analysis module 930 receives information from the lithography controller 140 of the scanner 115. The decision module 935 receives the outputs from the analyses modules (such as
20 the modules 925, 927, and 930) and determines which actuation module or modules need to be activated based on the outputs from the analyses modules. The light source actuation module 950 is connected to one or more of the optical source 105 and the spectral feature selection apparatus 130. The lithography actuation module 955 is connected to the scanner 115, and specifically to the lithography controller 140. The beam preparation actuation module 960 is connected to one
25 or more components of the beam preparation system 112.

While only a few modules are shown in Fig. 9, it is possible for the control system 185 to include other modules. Additionally, although the control system 185 is represented as a box in which all of the components appear to be co-located, it is possible for the control system 185 to be made up of components that are physically remote from each other. For example, the light
30 source actuation module 950 can be physically co-located with the optical source 105 or the spectral feature selection apparatus 130.

In general, the control system 185 receives at least some information about the light beam 110 from the measurement system 170, and the spectral feature analysis module 925 performs an analysis on the information to determine how to adjust one or more spectral features (for example, the bandwidth) of the light beam 110 supplied to the scanner 115. Based on this
5 determination, the control system 185 sends signals to the spectral feature selection apparatus 130 and/or the optical source 105 to control operation of the optical source 105 via the control module 550.

In general, the spectral feature analysis module 925 performs all of the analysis needed to estimate one or more spectral features (for example, the wavelength and/or the bandwidth) of the
10 light beam 110. The output of the spectral feature analysis module 925 is an estimated value of the spectral feature.

The spectral feature analysis module 925 includes a comparison block connected to receive the estimated spectral feature and also connected to receive a spectral feature target value. In general, the comparison block outputs a spectral feature error value that represents a
15 difference between the spectral feature target value and the estimated value. The decision module 935 receives the spectral feature error value and determines how best to effect a correction to the system 100 in order to adjust the spectral feature. Thus, the decision module 935 sends a signal to the light source actuation module 950, which determines how to adjust the spectral feature selection apparatus 130 (or the optical source 105) based on the spectral feature error value. The
20 output of the light source actuation module 950 includes a set of actuator commands that are sent to the spectral feature selection apparatus 130. For example, light source actuation module 950 sends the commands to the control module 550, which is connected to the actuation systems within the apparatus 530.

The control system 185 causes the optical source 105 to operate at a given repetition rate.
25 More specifically, the scanner 115 sends a trigger signal to the optical source 105 for every pulse (that is, on a pulse-to-pulse basis) and the time interval between those trigger signals can be arbitrary, but when the scanner 115 sends trigger signals at regular intervals then the rate of those signals is a repetition rate. The repetition rate can be a rate requested by the scanner 115.

The repetition rate of the pulses produced by the power amplifier 810 is determined by
30 the repetition rate at which the master oscillator 800 is controlled by the control system 185,

under the instructions from the controller 140 in the scanner 115. The repetition rate of the pulses output from the power amplifier 810 is the repetition rate seen by the scanner 115.

The prism 520 (or prism 620, 720) can be used for coarse, large range, slow bandwidth control. By contrast, the bandwidth can be controlled in a fine and narrow range and even more rapidly by controlling a differential timing between the activation of the electrodes within the MO 800 and the PRA 810.

Referring to Fig. 10, a procedure 1000 is performed by the photolithography system 100 to reduce the impact that stage vibrations (that is, vibrations of the stage 122) have on the CD on the wafer 120 to thereby improve the critical dimension uniformity (CDU).

The pulsed light beam 110 is produced (1005) for example, by the optical source 105. The pulsed light beam 110 is directed toward the wafer 120, which is mounted to the stage 122 of the scanner 115 (1010). For example, the pulsed light beam 110 produced by the optical source 105 is modified, as needed, and redirected by the beam preparation system 112 toward the scanner 115.

The pulsed light beam 110 is scanned across the wafer 120 (1015), for example, by moving the pulsed light beam 110 and the wafer 120 relative to each other along the lateral plane (the X_L - Y_L plane). Specifically, the lithography controller 140 can send one or more signals to the actuation systems associated with the wafer stage 122, the mask 134, and the objective arrangement 132 to thereby move one or more of the mask 134, the objective arrangement 132, and the wafer 120 (via the stage 122) relative to each other during the exposure to scan the exposure window 400 across an exposure field 223 of the wafer 220.

The value of the vibration of the stage 122 for each exposure field of a wafer is determined (1020). This determination can be performed at least in part by the metrology apparatus 145, and the output sent to the control system 185. This determination can be performed prior to scanning the wafer 120 with the pulsed light beam 110.

For each exposure field of the wafer 120, the control system 185 determines an amount of adjustment to a bandwidth of a pulsed light beam 110 directed toward the wafer 120 (1025). The adjustment amount compensates for a variation in the stage vibration in that exposure field outside of an acceptable range and maintains the focus blur within a predetermined range of values across the entire wafer 120. Next, and as the pulsed light beam 110 is being scanned across the wafer 120, the control system 185 sends a signal to the spectral feature selection

apparatus 130 to change the bandwidth of the pulsed light beam 110 by the determined adjustment amount for each exposure field of the wafer 120 (1035).

Additionally, during the procedure 1000, the control system 185 also performs a parallel procedure 1040 for controlling one or more spectral features of the pulsed light beam 110 while the light beam 110 is being scanned across the wafer 120. The procedure 1040 includes measuring one or more spectral features of the pulsed light beam 110 (1045) and determining whether any of the measured spectral features are outside of an acceptable range of values (1050). For example, the spectral feature analysis module 925 of the control system 185 can receive the spectral feature measurement from the measurement system 170 (1045). The spectral feature analysis module 925 can determine whether any of the spectral features are outside an acceptable range of values (1050). If any of the spectral features are outside an acceptable range of values, then those spectral features are adjusted (1055). For example, the decision module 935 can send a signal to the light source actuation module 950, which sends a signal to the spectral feature selection apparatus 130 to adjust one or more spectral features of the light beam 110 (1055).

The procedure 1040 can be performed in parallel with the procedure 1000, for example, during the scanning or at regular intervals, for example, for each exposure field 223. Moreover, it is possible for the control system 185 to coordinate the adjustment to the bandwidth needed to compensate for the stage vibration variation (1030) with any required adjustment to the bandwidth to ensure that the bandwidth is within an acceptable range of values (1055).

Referring to Fig. 11, the photolithography system 100 can perform a procedure 1025 for determining an amount of adjustment to the bandwidth of the pulsed light beam 110 directed toward the wafer 120 for a particular sub-area (such as an exposure field) of the wafer 120. Such adjustment amount compensates for a variation in the stage vibration in that exposure field outside of an acceptable range and maintains the focus blur within a predetermined range of values across the entire wafer 120. The procedure 1025 can be performed by the control system 185. The control system 185 accesses a lookup table (1126). The lookup table is a table or correction map that is created based on previously determined stage vibration for the scanner 115 and it defines a relationship between the bandwidth of the light beam 110 for each sub-area of the wafer 120, the value of the bandwidth being selected to offset the measured value of the stage vibration in that sub-area. The stage vibration values depend on the scanner 115 and wafer stage

122 being used. Thus, the relationship between stage vibration and the sub-area of a wafer 120 for one particular scanner 115 and stage 122 may be different than the relationship for another particular scanner 115 and stage 122.

Fig. 12 shows an example of how the lookup table can be created. Initially, a wafer 120 is placed in the scanner 115, and the metrology apparatus 145 probes the wafer 120 at each sub-area to determine the stage vibration in the direction Z_L for each sub-area of the wafer 120. Graph 1200 shows an exemplary relationship between the number of occurrences (frequencies) of various stage vibrations in Z_L for all sub-areas of the wafer 120. In this example, the stage vibration in Z_L is the moving standard deviation (MSD) value along the Z_L direction at each wafer sub-area (which can correspond to a wafer exposure field 223). This graph 1200 shows that, in this example, the nominal $MSD(Z_L)$ value occurs at a much higher frequency than a higher $MSD(Z_L)$ value from the center of the wafer 120 to the edge of the wafer 120. The control system 185 seeks to maintain an effective stage vibration SVE at a constant value. The effective stage vibration is related to the measured stage vibration (SVM) (such as that shown in graph 1200) and the bandwidth (BW) of the pulsed light beam 110) as follows:

$$SVE = \sqrt{SVM^2 + (BW \cdot CA)^2},$$

where CA is the chromatic aberration experienced by the pulsed light beam 110 as it is directed toward the wafer 120. Thus, the control system 185 can calculate the BW after the graph 1200 is obtained so as to maintain a constant value of the effective stage vibration. Graph 1250 shows the values of the BW of the light beam 110 that can be used to offset the measured stage vibration SVM and maintain the effective stage vibration SVE constant.

The control system 185 reviews the lookup table (such as the graph 1500) and determines the bandwidth that compensates for the measured stage vibration in that wafer sub-area so as to maintain an effective stage vibration constant in that sub-area (1028) and then outputs this value of the determined bandwidth (1030).

In some implementations, the lookup table can be created by the metrology apparatus 145 prior to directing the pulsed light beam 110 toward the wafer 120 that is currently mounted to the stage 122. Thus, the lookup table can be created based on a prior scanned wafer 120.

Other implementations are within the scope of the following claims.

What is claimed is:

1. A method comprising:

producing, from the pulsed optical source, a pulsed light beam;

directing the pulsed light beam toward a substrate mounted to a stage of a lithography

5 exposure apparatus;

performing a scanning operation between the pulsed light beam and the substrate,

wherein the scanning operation comprises projecting the pulsed light beam onto each sub-area of the substrate and moving one or more of the pulsed light beam and the substrate relative to each other;

10 determining a value of a vibration of the stage for each sub-area of a substrate;

for each sub-area of the substrate, determining an amount of adjustment to a bandwidth of the pulsed light beam, the adjustment amount compensating for a variation in the stage vibration so as to maintain a focus blur within a predetermined range of values across the substrate; and

15 changing the bandwidth of the pulsed light beam by the determined adjustment amount as the pulsed light beam is exposing a substrate to thereby compensate for the stage vibration variations.

2. The method of claim 1, wherein determining the amount of adjustment to the
20 bandwidth in a particular sub-area comprises accessing a lookup table to determine a value of the bandwidth that maintains an effective stage vibration constant.

3. The method of claim 2, further comprising creating the lookup table prior to directing the pulsed light beam toward the substrate.

25

4. The method of claim 1, wherein determining the value of the stage vibration for each sub-area of a substrate comprises determining the value of the stage vibration for each sub-area of the substrate after a scanning operation has been performed between the pulsed light beam and the substrate.

30

5. The method of claim 4, wherein changing the bandwidth of the pulsed light beam by the determined adjustment amount as the pulsed light beam is exposing a substrate comprises changing the bandwidth of the pulsed light beam by the determined adjustment amount as the pulsed light beam is exposing a substrate that has not yet been scanned by the pulsed light beam.

5

6. The method of claim 1, wherein determining the amount of adjustment to the bandwidth of the pulsed light beam occurs prior to directing the pulsed light beam toward the substrate.

10 7. The method of claim 1, wherein determining the amount of adjustment to the bandwidth of the pulsed light beam occurs while the pulsed light beam is directed toward the substrate and at each sub-area of the substrate.

15 8. The method of claim 1, wherein changing the bandwidth of the pulsed light beam comprises adjusting one or more optical components of a spectral feature selection apparatus.

9. The method of claim 8, wherein adjusting one or more optical components of the spectral feature selection apparatus comprises rotating and translating a prism of the spectral feature selection apparatus.

20

10. The method of claim 1, wherein maintaining the focus blur within the predetermined range also maintains a critical dimension of a feature formed in the substrate to within a predetermined range.

25 11. The method of claim 1, wherein changing the bandwidth of the pulsed light beam comprises changing the bandwidth in between bursts of pulses of the pulsed light beam.

12. The method of claim 1, further comprising measuring a bandwidth of the pulsed light beam that is directed toward the substrate, and adjusting the bandwidth of the pulsed light beam if the measured bandwidth is outside an acceptable range of bandwidths.

30

13. An apparatus comprising:

an optical source producing a pulsed light beam;

a beam directing system directing the pulsed light beam toward a substrate mounted to a stage of a lithography exposure apparatus;

5 a scanning system configured to project the pulsed light beam onto each sub-area of the substrate and move one or more of the pulsed light beam and the substrate relative to each other;

a metrology apparatus configured to determine a value of a vibration of the stage for each sub-area of a substrate; and

10 a control system connected to the optical source, the scanning system, and the metrology apparatus, and configured to:

receive the determined values of the stage vibration for each sub-area from the metrology apparatus;

15 for each sub-area, determine an amount of adjustment to a bandwidth of the pulsed light beam, the adjustment amount compensating for a variation in the stage vibration so as to maintain a focus blur within a predetermined range of values across the substrate; and

send a signal to the optical source to modify the bandwidth of the pulsed light beam by the determined adjustment amount as the pulsed light beam is exposing a substrate to thereby compensate for the stage vibration variation.

20

14. The apparatus of claim 13, wherein the scanning system is configured to move one or more of the pulsed light beam and the substrate relative to each other along a lateral plane.

25 15. The apparatus of claim 14, wherein the lateral plane is perpendicular to an axial direction along which the pulsed light beam is directed, and the metrology apparatus is configured to determine the value of the vibration of the stage along the axial direction.

30 16. The apparatus of claim 13, further comprising a spectral feature selection apparatus configured to select a spectral feature of the pulsed light beam, the spectral feature selection apparatus comprising a set of optical components arranged in the path of the pulsed light beam, wherein the control system is connected to the spectral feature selection apparatus.

17. The apparatus of claim 16, wherein the control system sends a signal to the optical source to modify the bandwidth of the pulsed light beam by sending a signal to the spectral feature selection apparatus to move at least one optical component to thereby change the bandwidth of the pulsed light beam.

18. The apparatus of claim 17, wherein the set of optical components of the spectral feature selection apparatus comprises at least one prism, and the control system sends the signal to the spectral feature selection apparatus to move the at least one optical component to thereby change the bandwidth of the pulsed light beam by sending a signal to a rapid actuator associated with the at least one prism to cause the prism to rotate to thereby change the bandwidth.

19. The apparatus of claim 16, wherein the set of optical components of the spectral feature selection apparatus comprises:

a dispersive optical element arranged to interact with the pulsed light beam, and a plurality of prisms arranged in the path of the pulsed light beam between the dispersive optical element and the optical source.

20. The apparatus of claim 16, wherein the spectral feature selection apparatus comprises an actuation system comprising at least one rapid actuator associated with a prism and configured to rotate the associated prism to thereby adjust a spectral feature of the pulsed light beam.

21. The apparatus of claim 20, wherein the rapid actuator comprises a rotation stage that rotates about a rotation axis and includes a region that is mechanically linked to the prism.

22. The apparatus of claim 21, wherein the rotation stage is configured to rotate about the rotation axis along a full 360° of angle of rotation.

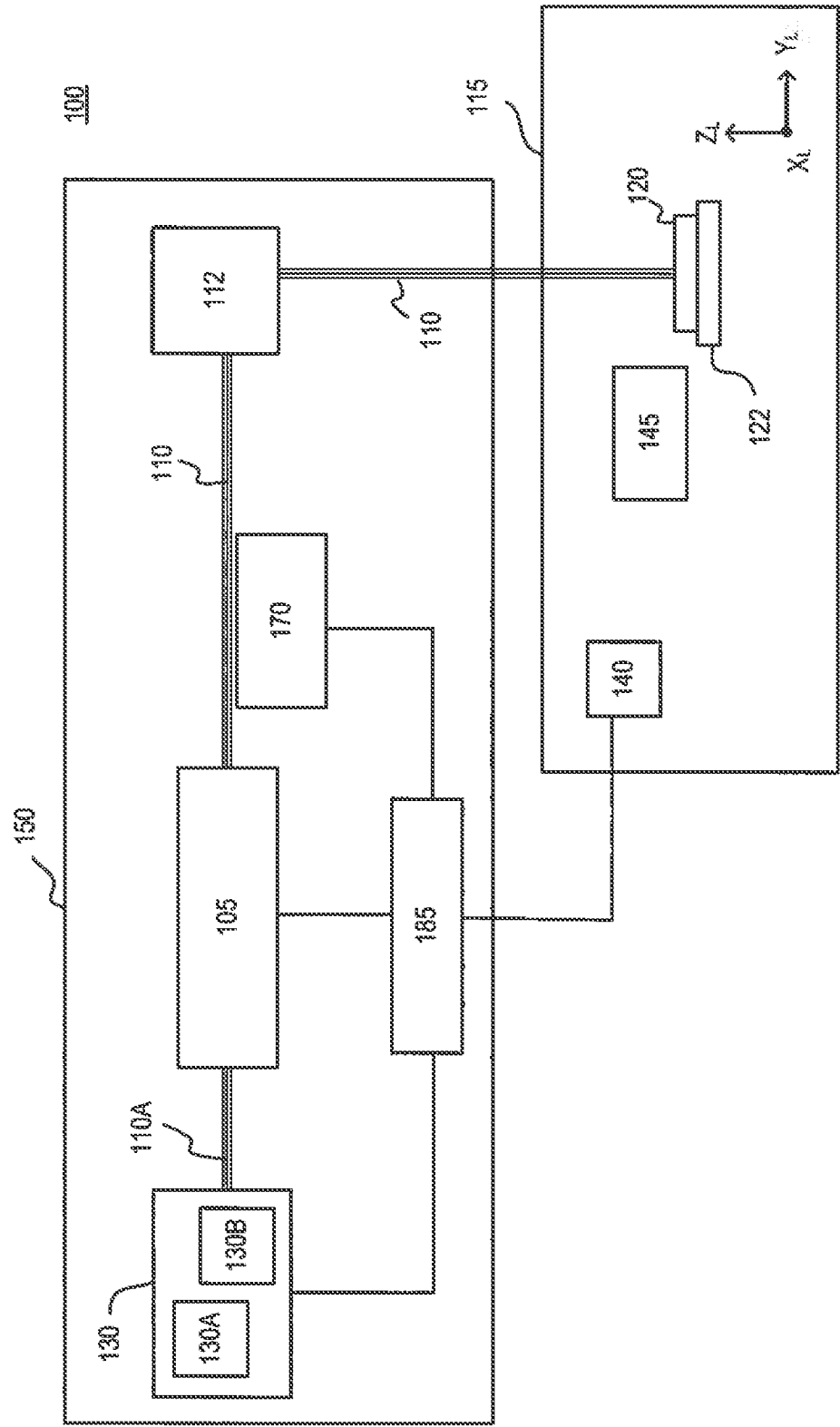


Fig. 1

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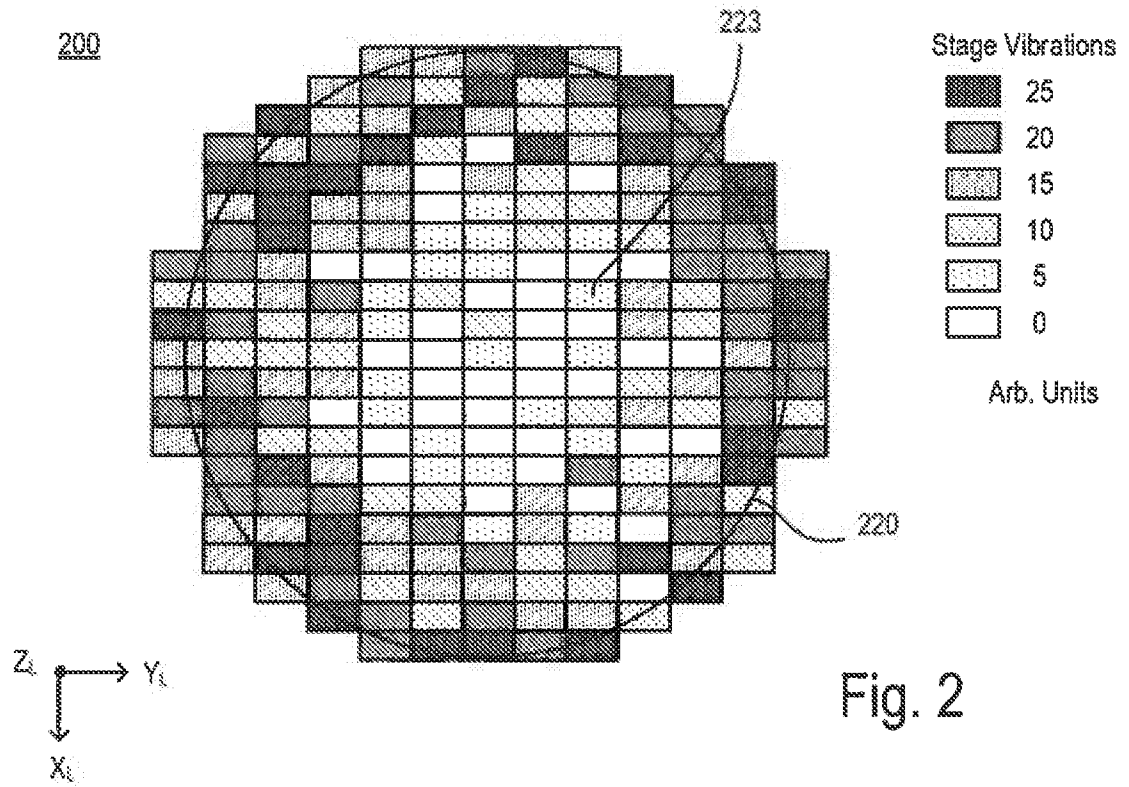


Fig. 2

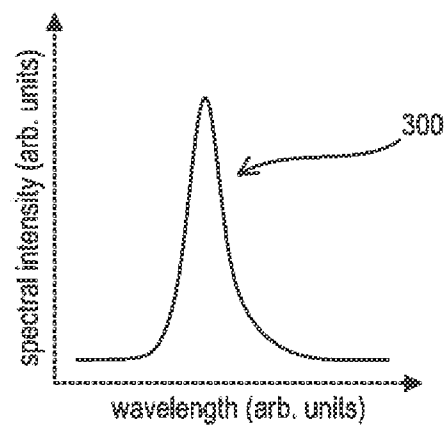
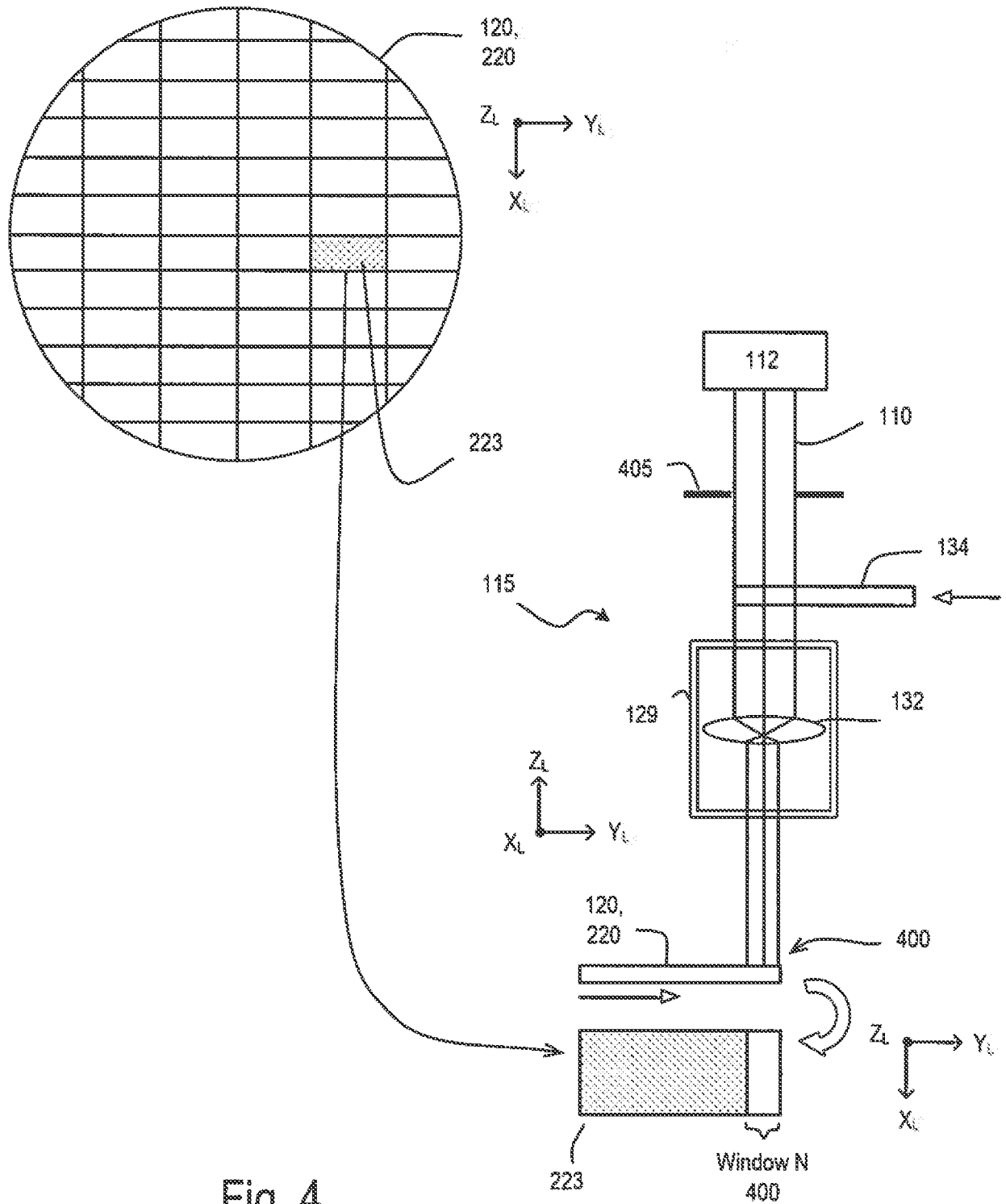
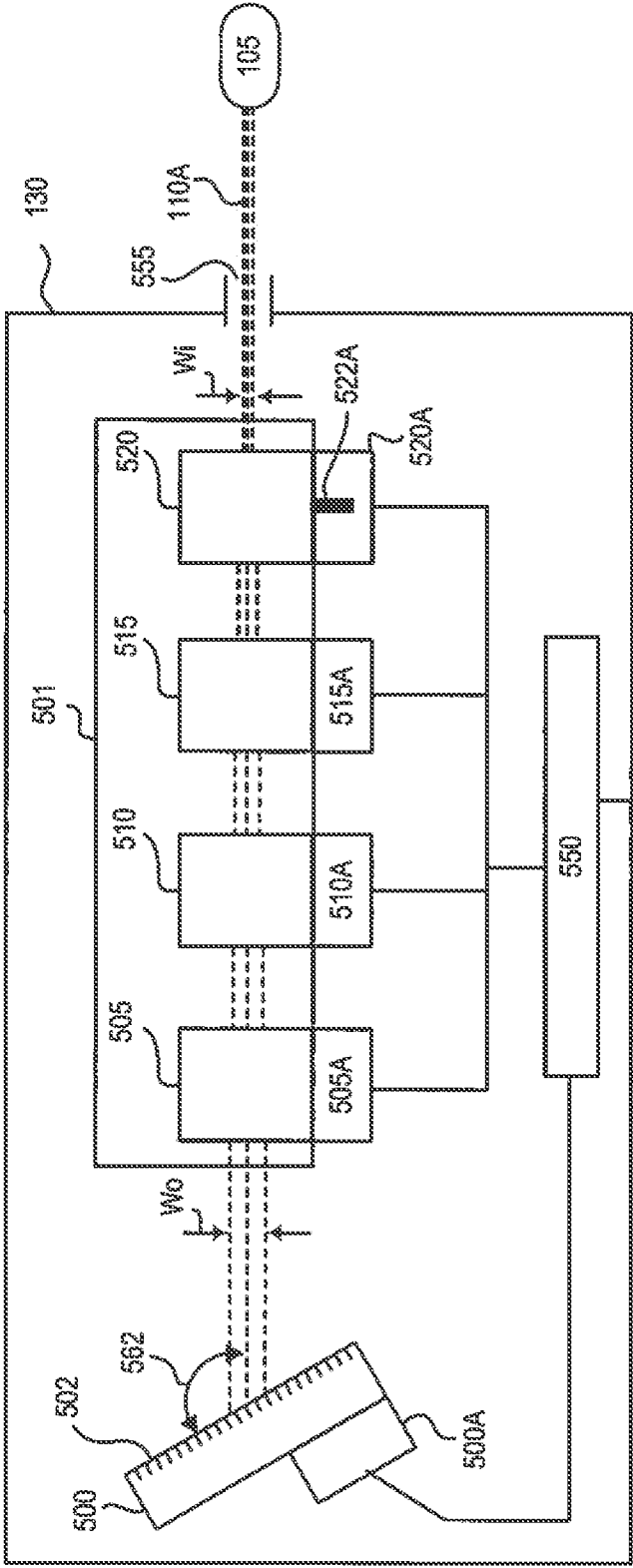


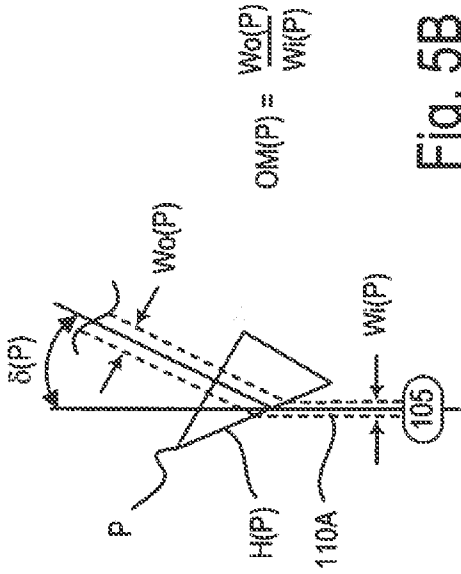
Fig. 3

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565 $OM = \frac{W_0}{W_i}$ Fig. 5A



$$OM(P) = \frac{W_0(P)}{W_i(P)}$$

Fig. 5B

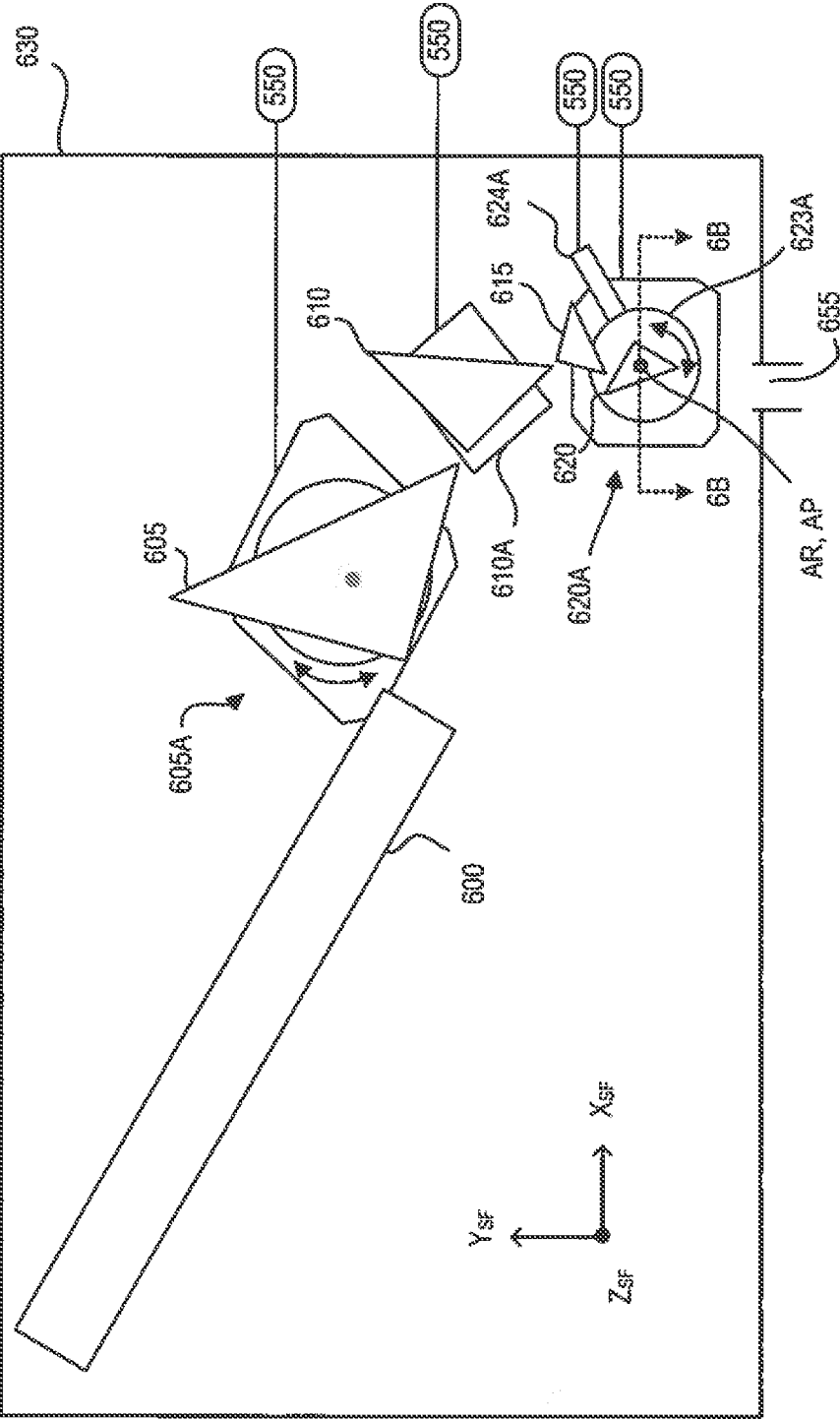


Fig. 6A

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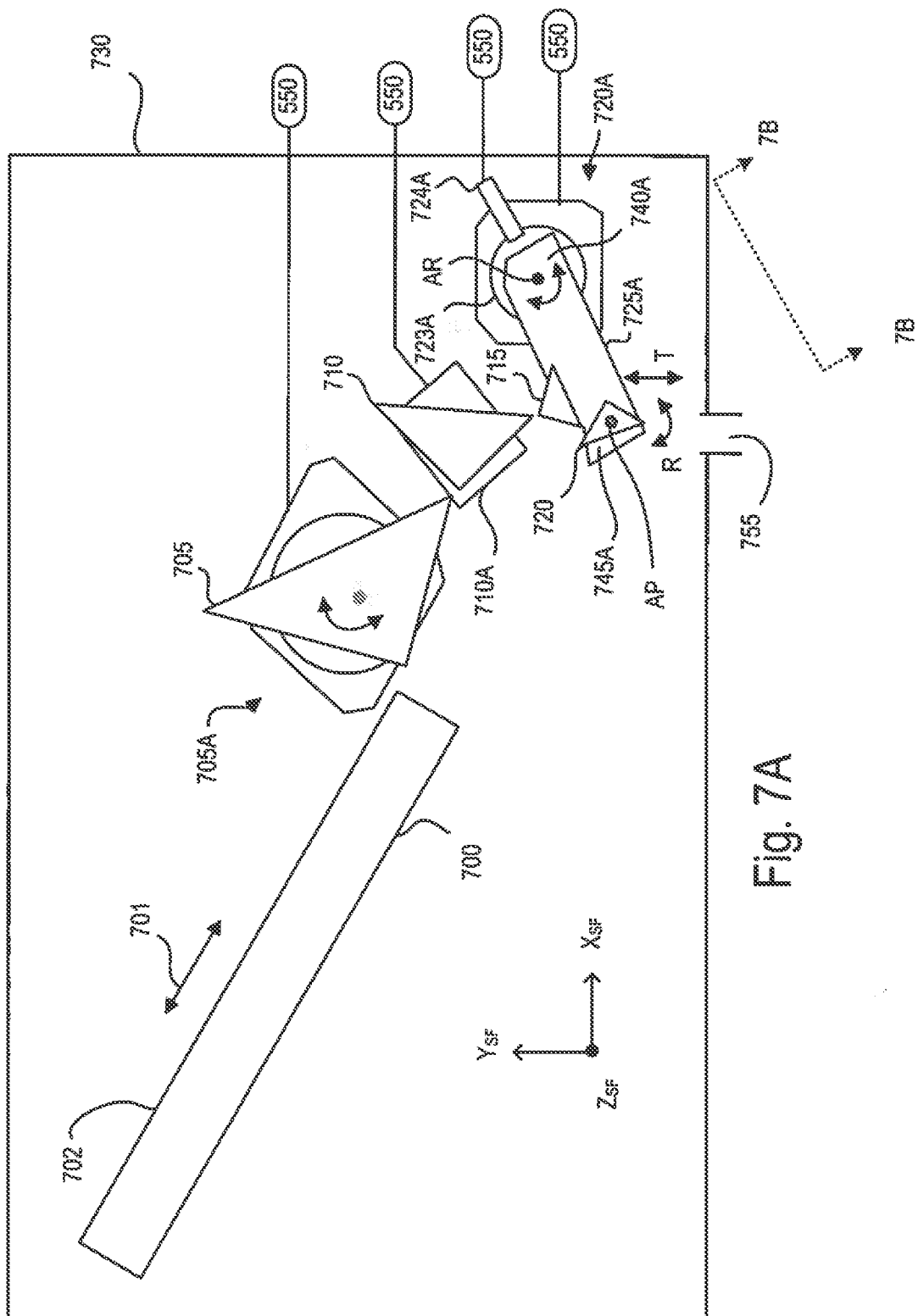
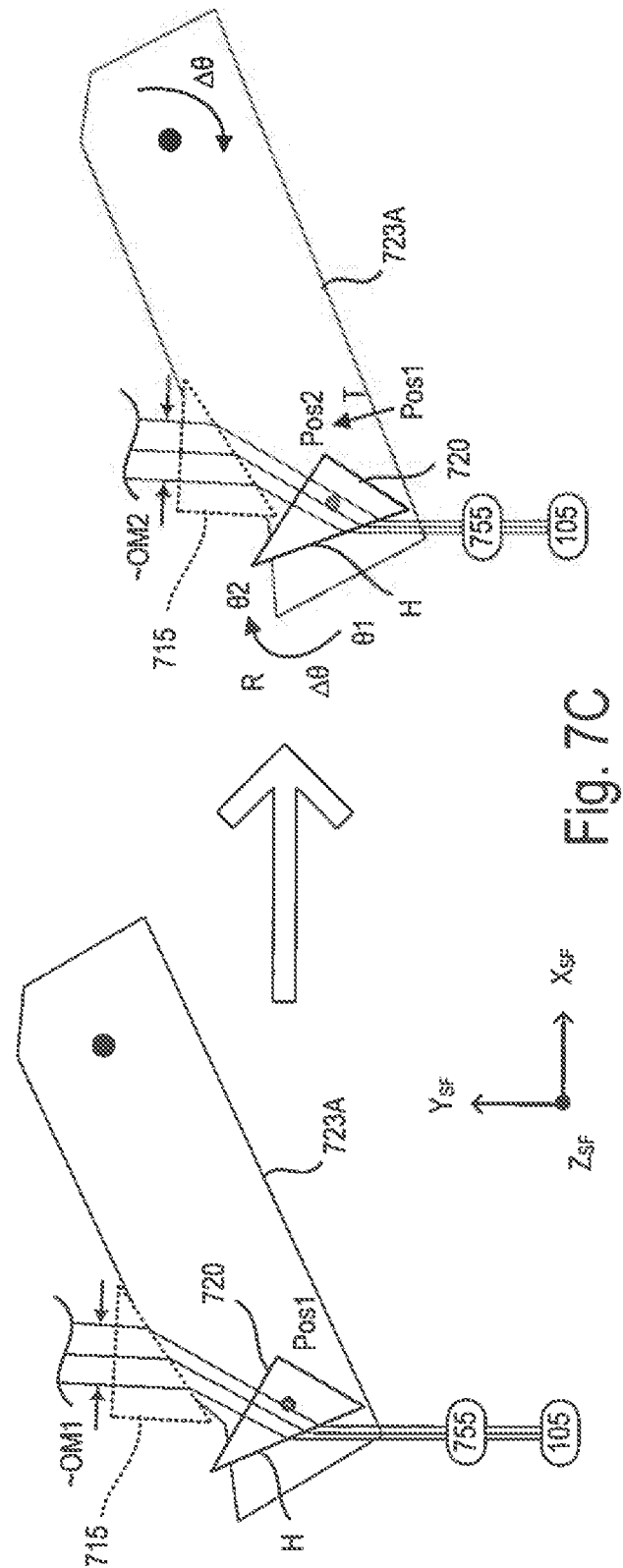
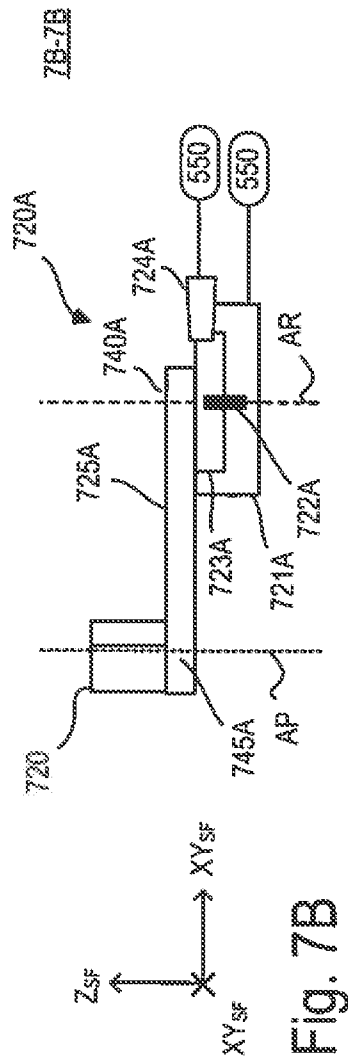


Fig. 7A



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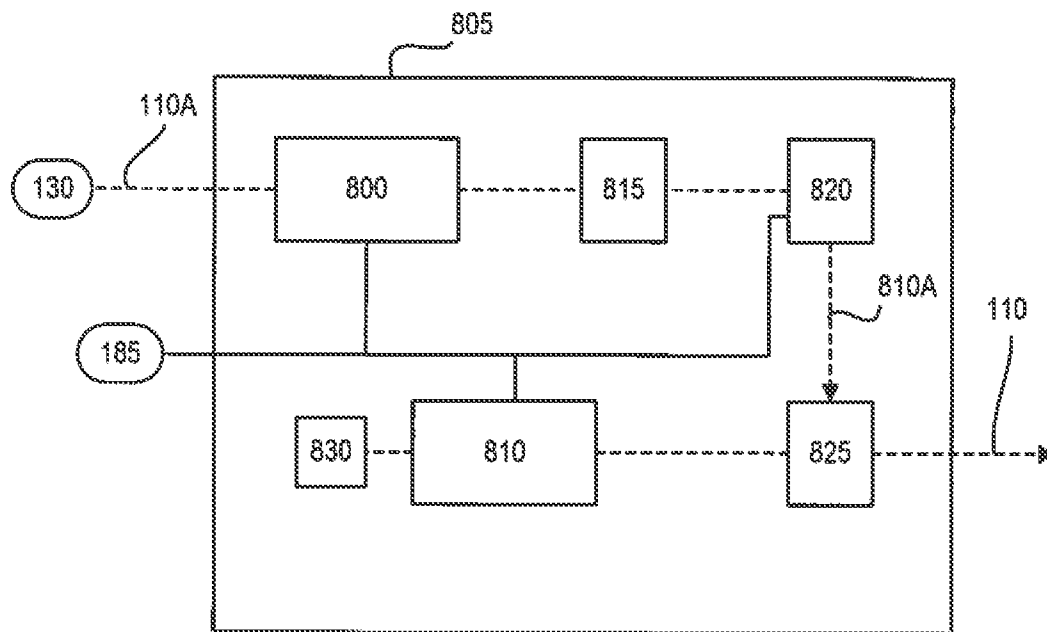


Fig. 8

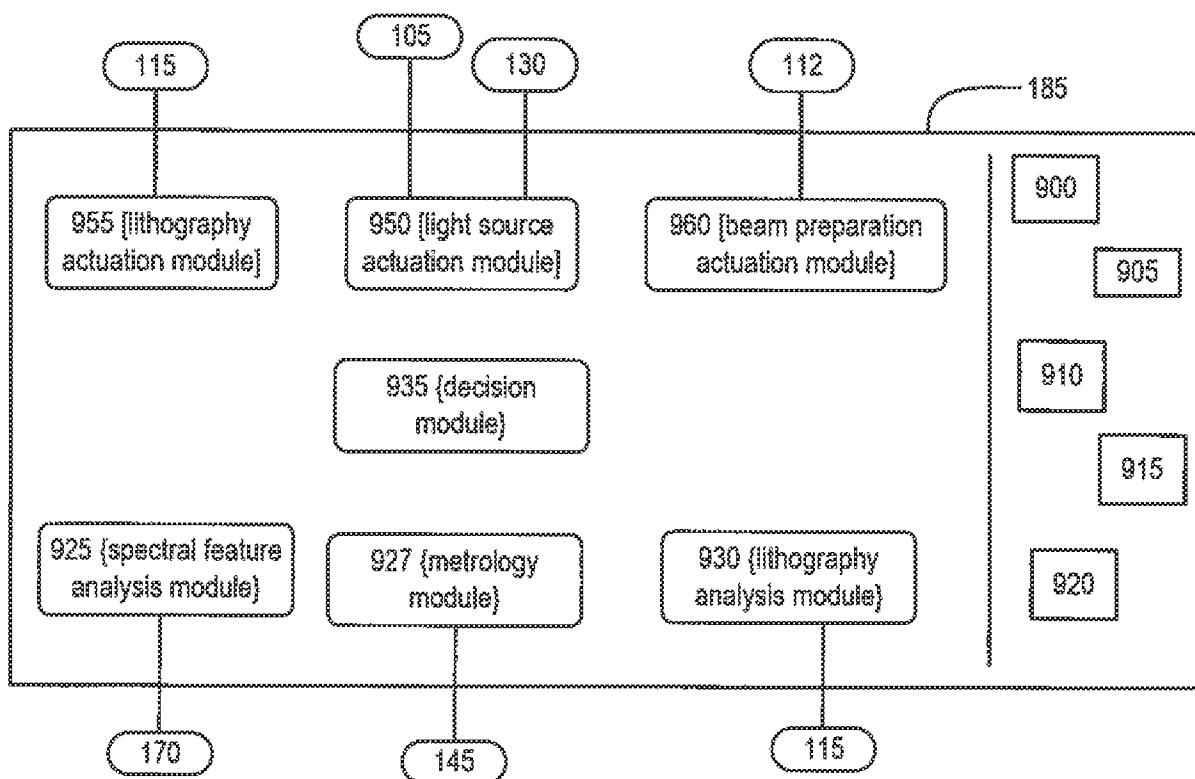


Fig. 9

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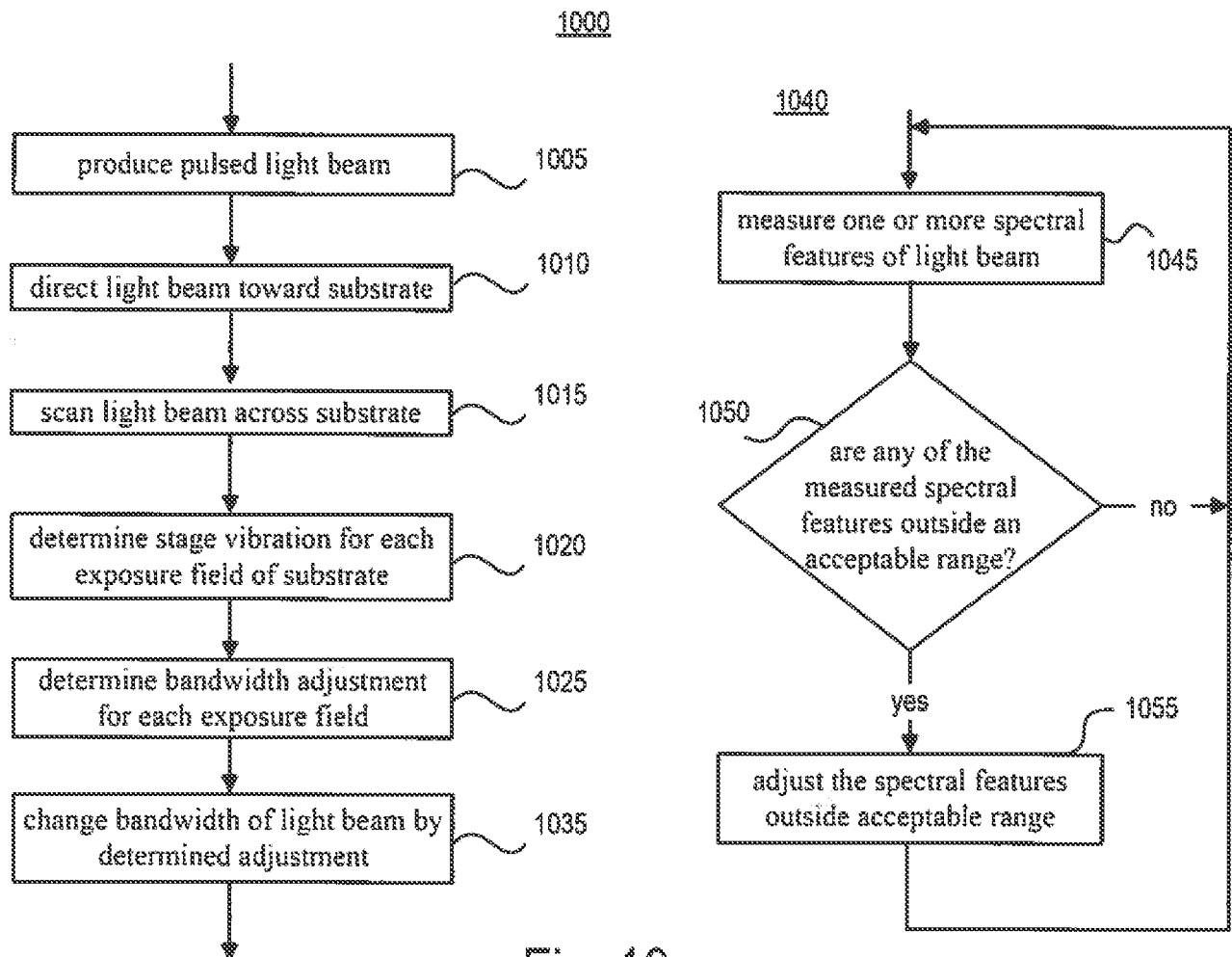


Fig. 10

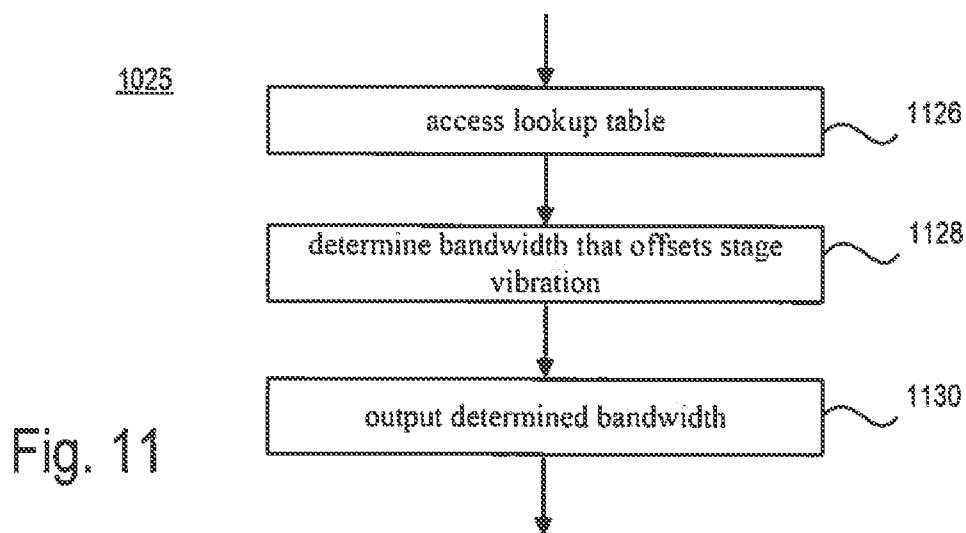


Fig. 11

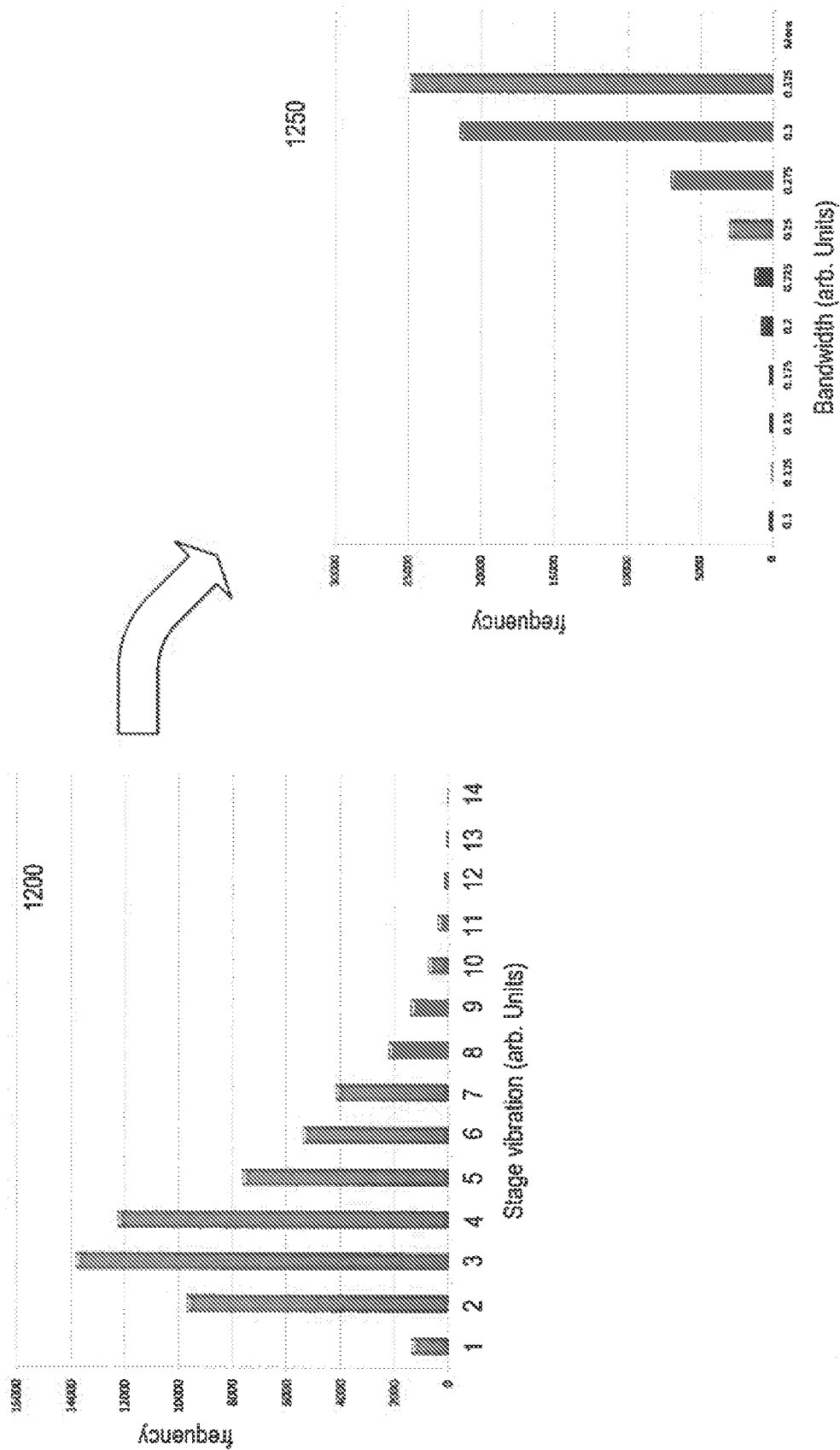


Fig. 12

INTERNATIONAL SEARCH REPORT		International application No. PCT/US17/55141		
A. CLASSIFICATION OF SUBJECT MATTER IPC: G03F 7/20 (2006.01) CPC: G03F 7/70716, 7/707, 7/70758, 7/709; G03B 27/582 According to International Patent Classification (IPC) or to both national classification and IPC				
B. FIELDS SEARCHED				
Minimum documentation searched (classification system followed by classification symbols) CPC. : G03F 7/70716, 7/707, 7/70758, 7/709; G03B 27/582				
Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched				
Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)				
C. DOCUMENTS CONSIDERED TO BE RELEVANT				
Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.		
A	US 2015/0355025 A1 (Duffey et al.) 10 December 2015, see entire document.	1-22		
A	US 2015/0168848 A1(TANAKA et al.) 18 June 2015, see entire document.	1-22		
☐ Further documents are listed in the continuation of Box C. ☐ See patent family annex.				
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Date of the actual completion of the international search 23 October 2017 (23.10.2017)		Date of mailing of the international search report 27 OCT 2017		
Name and mailing address of the ISA/US Mail Stop PCT, Attn: ISA/US Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450 Facsimile No. (571) 273-8300		Authorized officer Seungsook Ham Telephone No. 571-272-4300		